

Microarchitecture and Design Challenges for Gigascale Integration

Shekhar Borkar

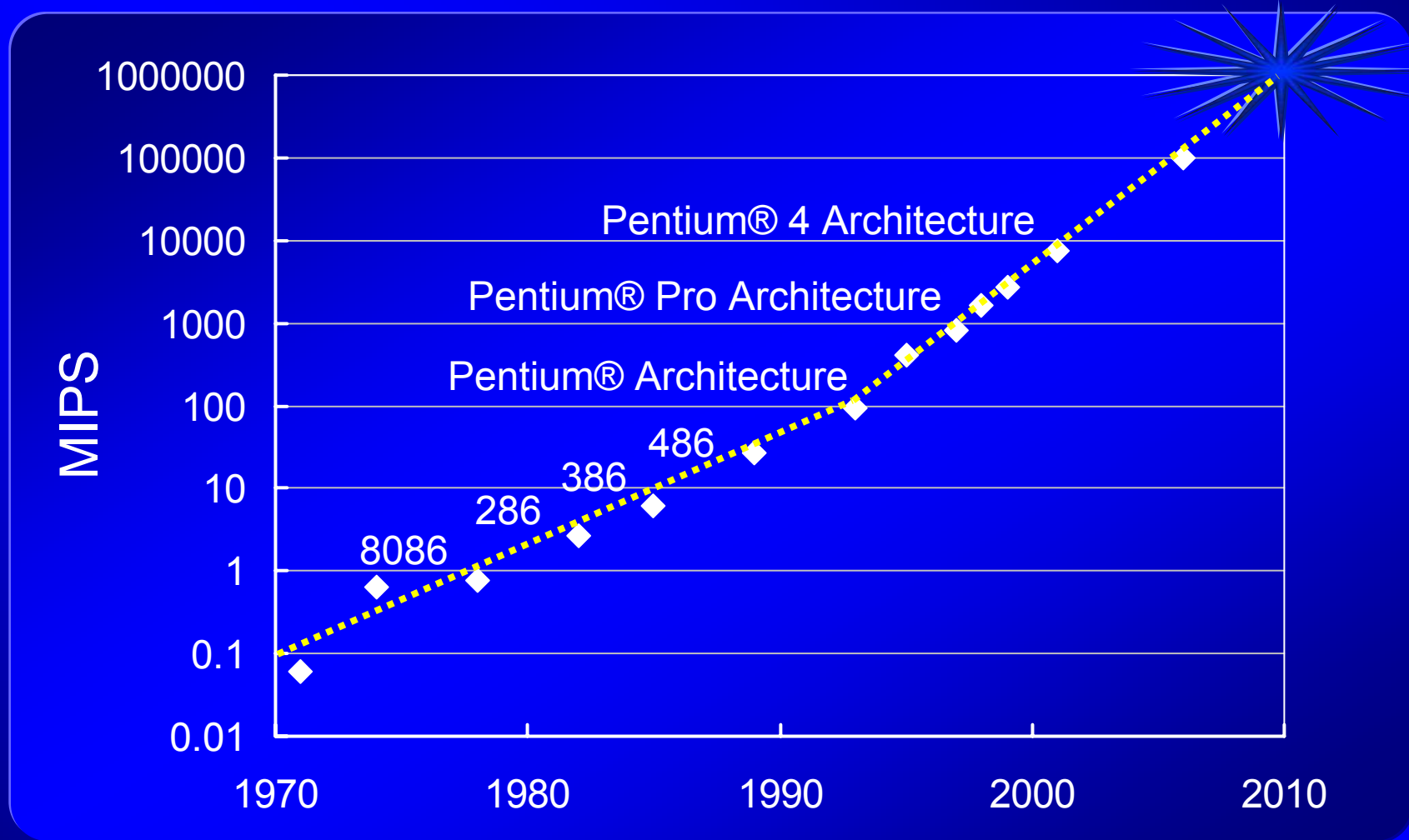
Intel Corp.

December 6, 2004

Outline

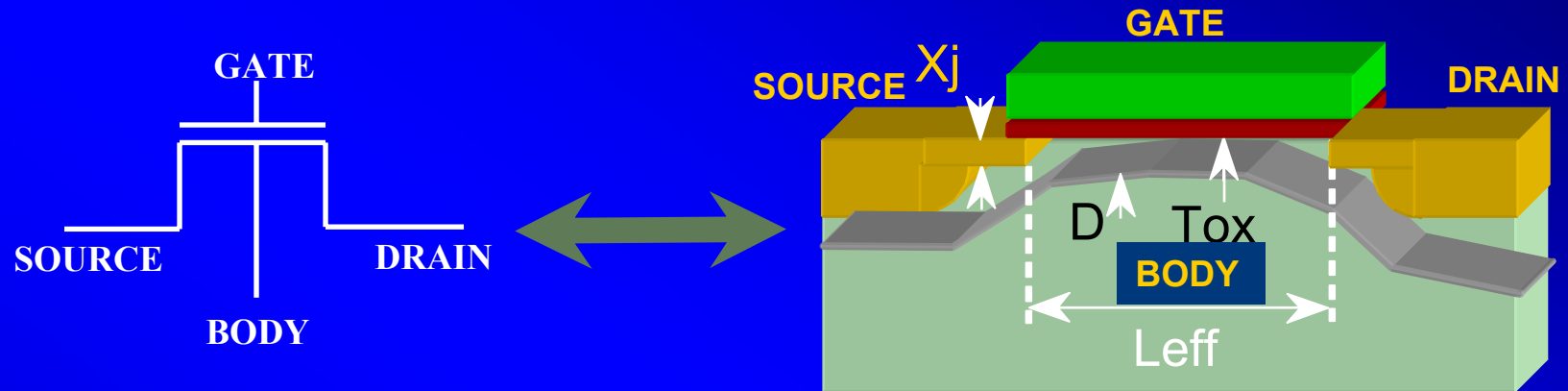
- **Process technology scaling & near term challenges**
- **μArchitecture & Design solutions**
- **Upcoming paradigm shifts**
- **Long term outlook & challenges**
- **Summary**

Goal: 1TIPS by 2010



How do you get there?

Technology Scaling



Dimensions scale down by 30%	Doubles transistor density
Oxide thickness scales down	Faster transistor, higher performance
Vdd & Vt scaling	Lower active power

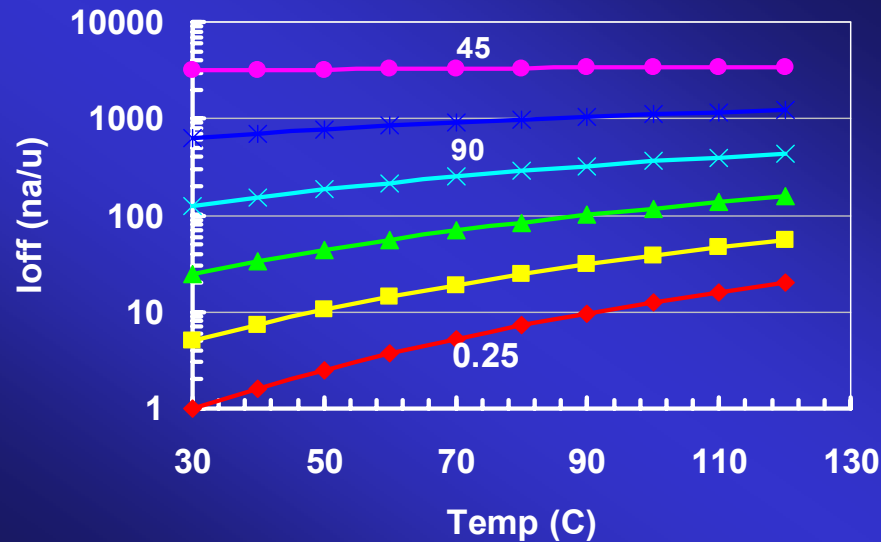
Scaling will continue, but with challenges!

Technology Outlook

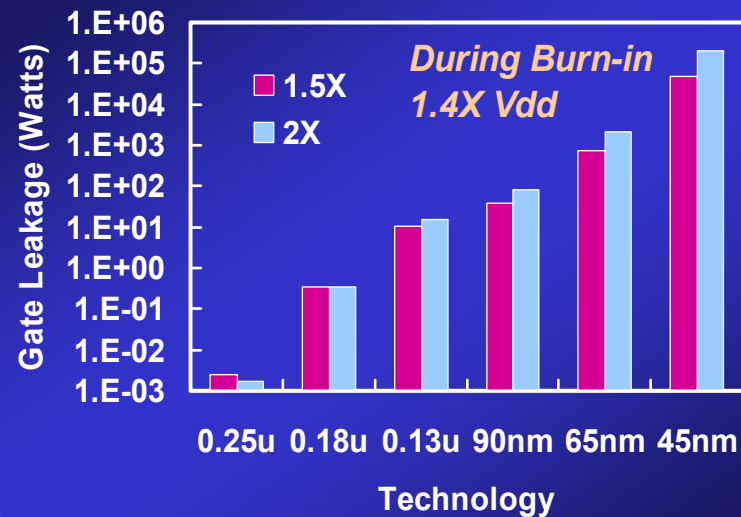
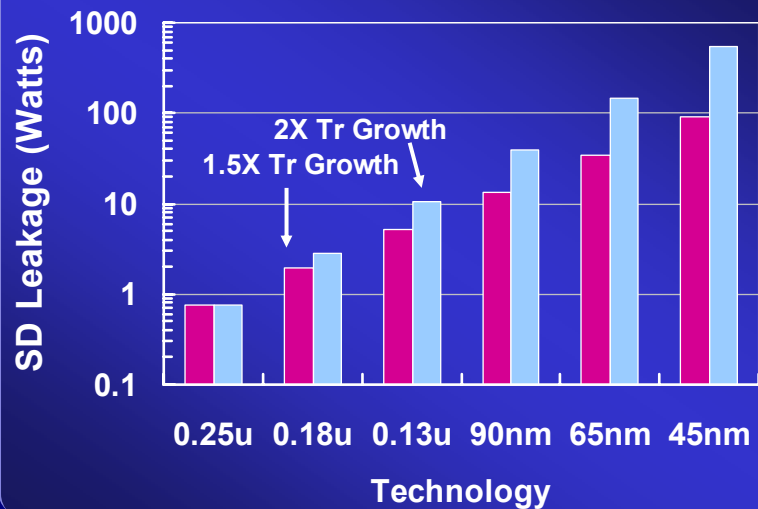
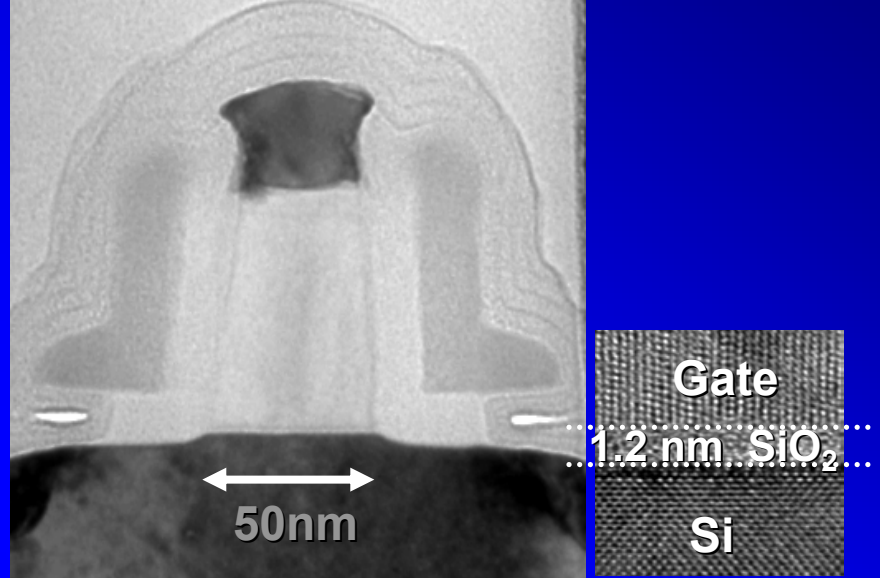
High Volume Manufacturing	2012	2014	2016	2018
Technology Node (nm)	22	16	11	8
Integration Capacity (BT)	32	64	128	256
Delay = CV/I scaling	Delay scaling will slow down			
Energy/Logic Op scaling	Energy scaling will slow down			
Bulk Planar CMOS	Low Probability			
Alternate, 3G etc	High Probability			
Variability	Very High			
ILD (K)	Increase slowly towards 2-2.5			
RC Delay	1	1	1	1
Metal Layers	to 1 layer per generation			

POWER & ENERGY

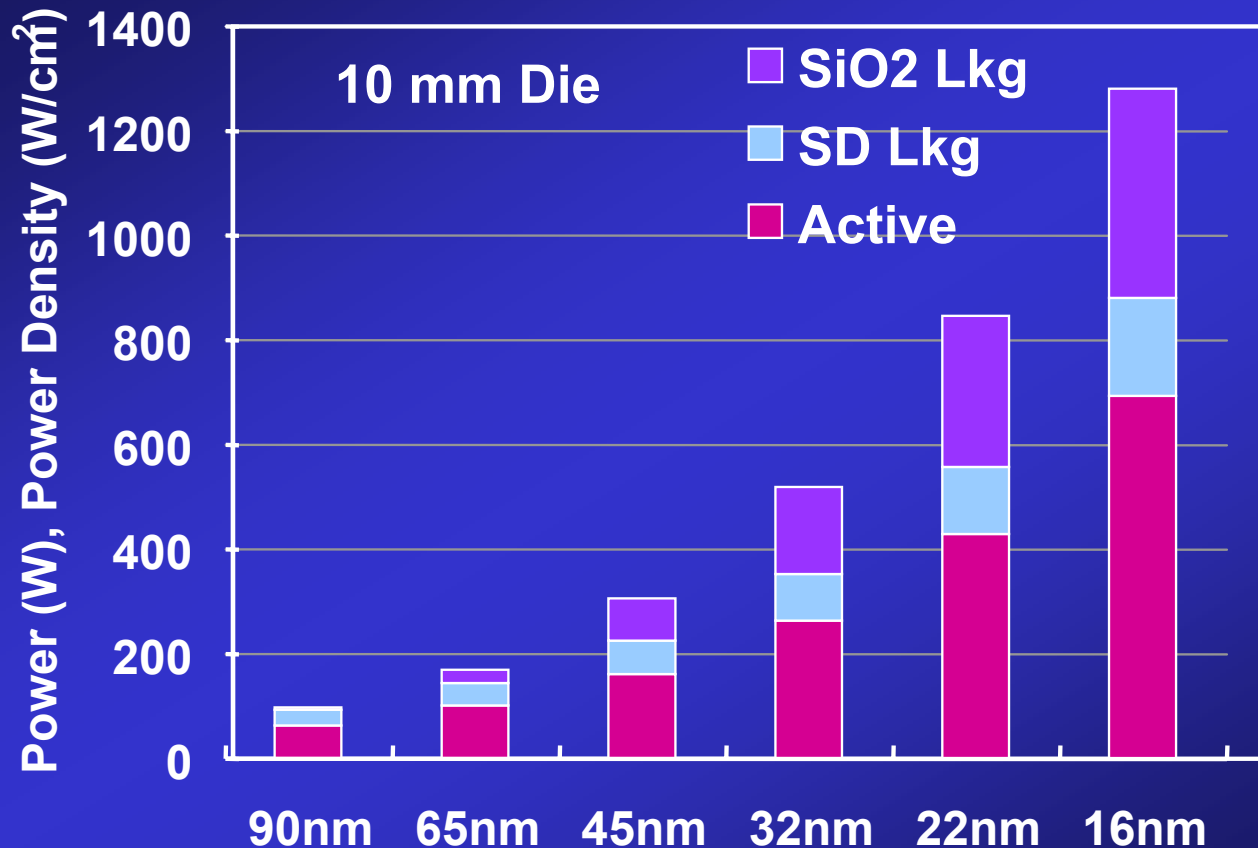
The Leakage(s)...



90nm MOS Transistor

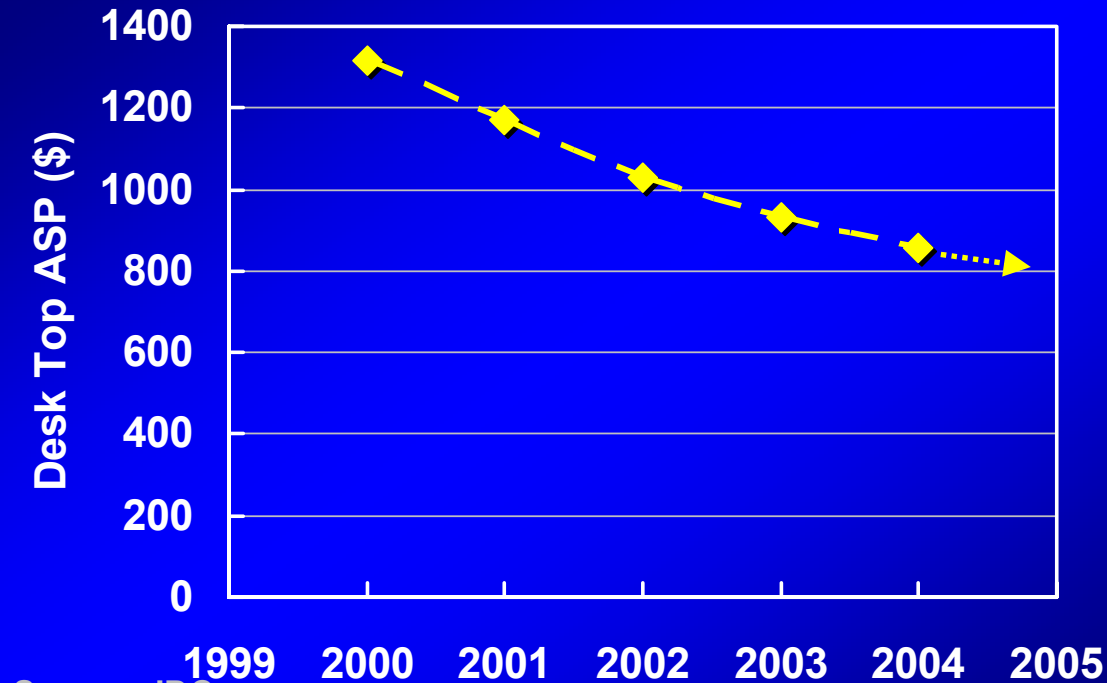


Projected Power (unconstrained)

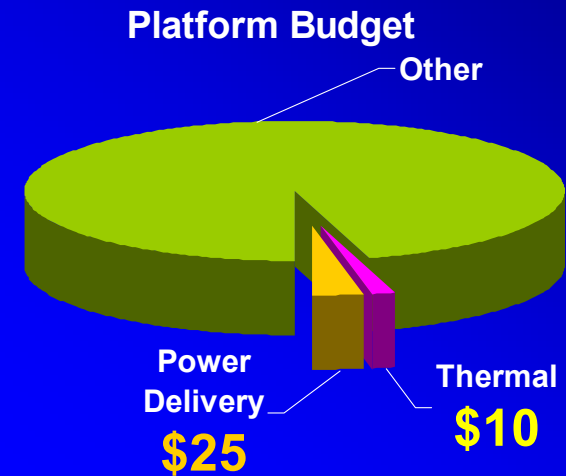


Active and Leakage power will become prohibitive

Product Cost Pressure

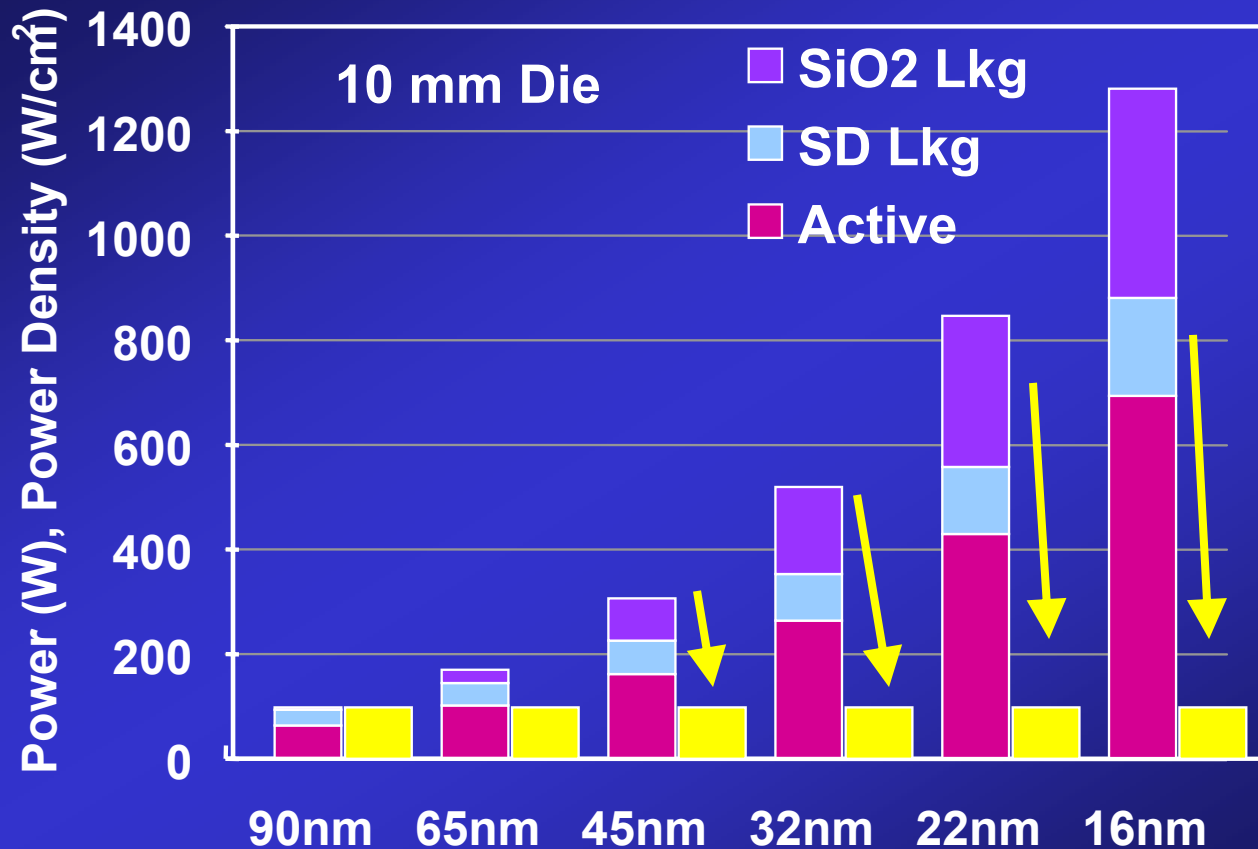


Source: IDC



Shrinking ASP, and shrinking \$ budget for power

Must Fit in Power Envelope



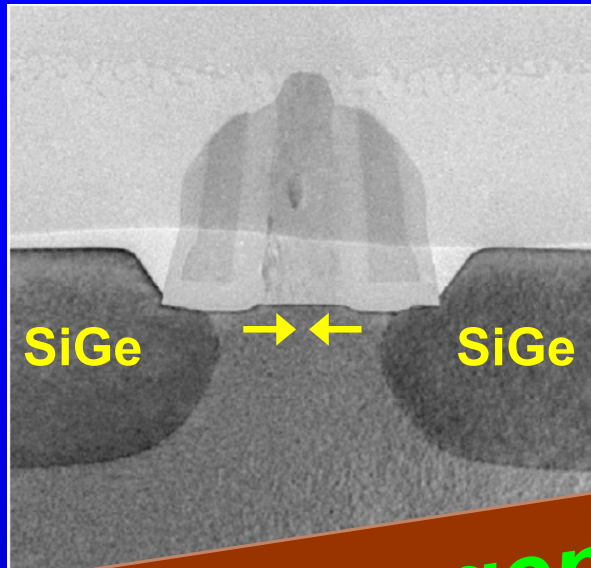
**Technology, Circuits, and
Architecture to constrain the power**

Between Now and Then—

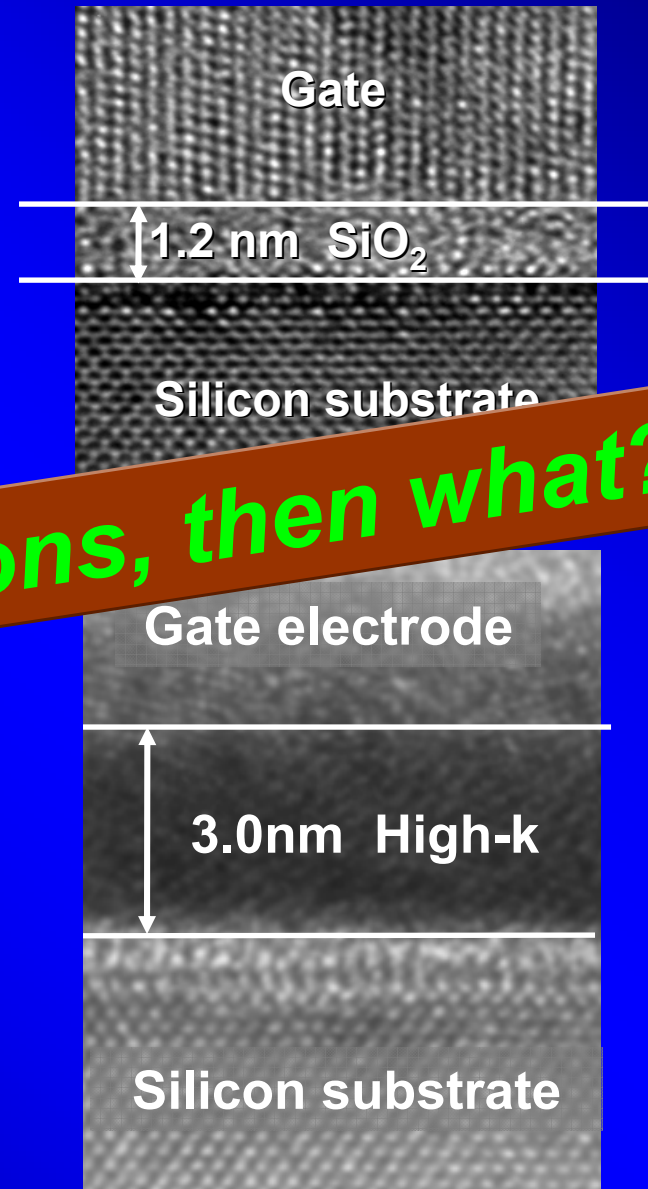
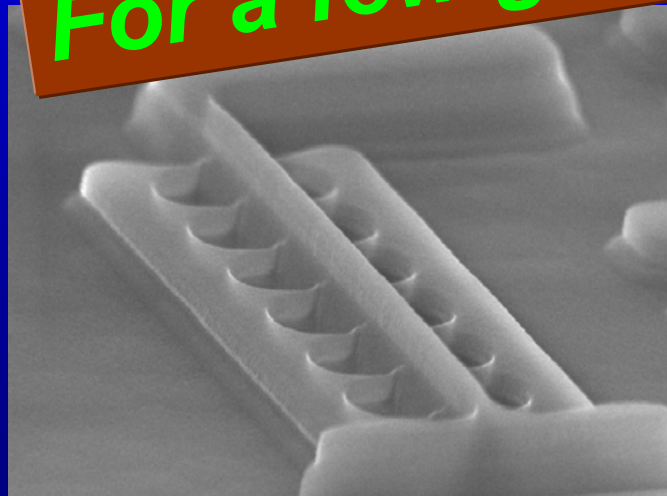
- **Move away from Frequency alone to deliver performance**
- **More on-die memory**
- **Multi-everywhere**
 - Multi-threading
 - Chip level multi-processing
- **Throughput oriented designs**
- **Valued performance by higher level of integration**
 - Monolithic & Polyolithic

Leakage Solutions

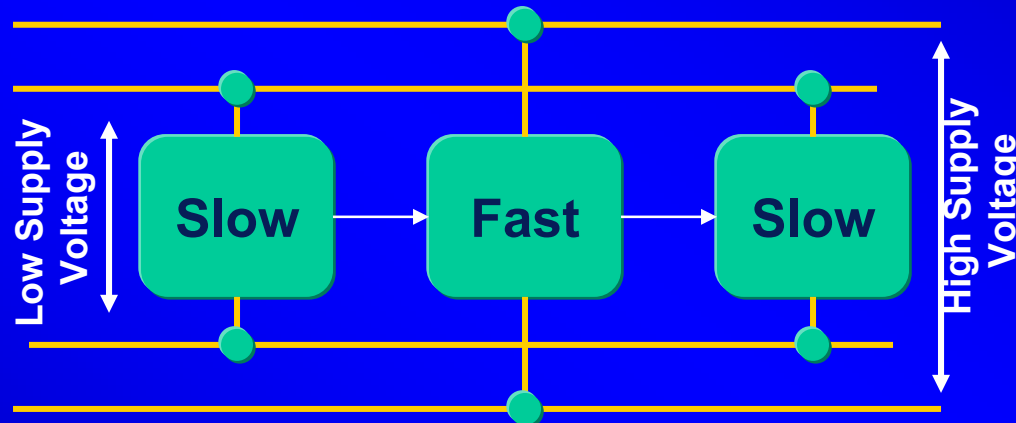
Planar Transistor



For a few generations, then what?

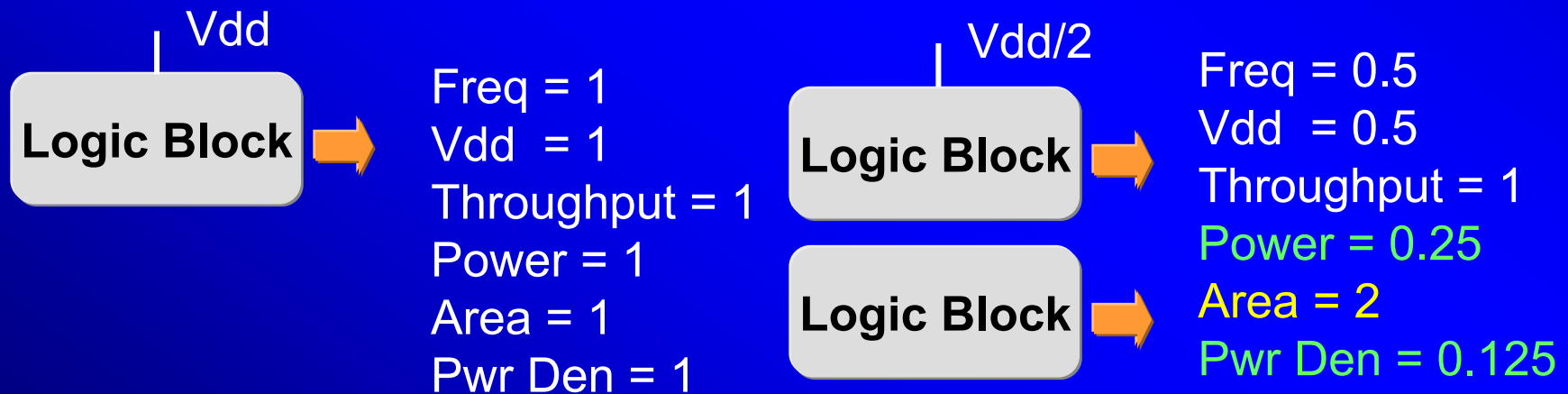


Active Power Reduction



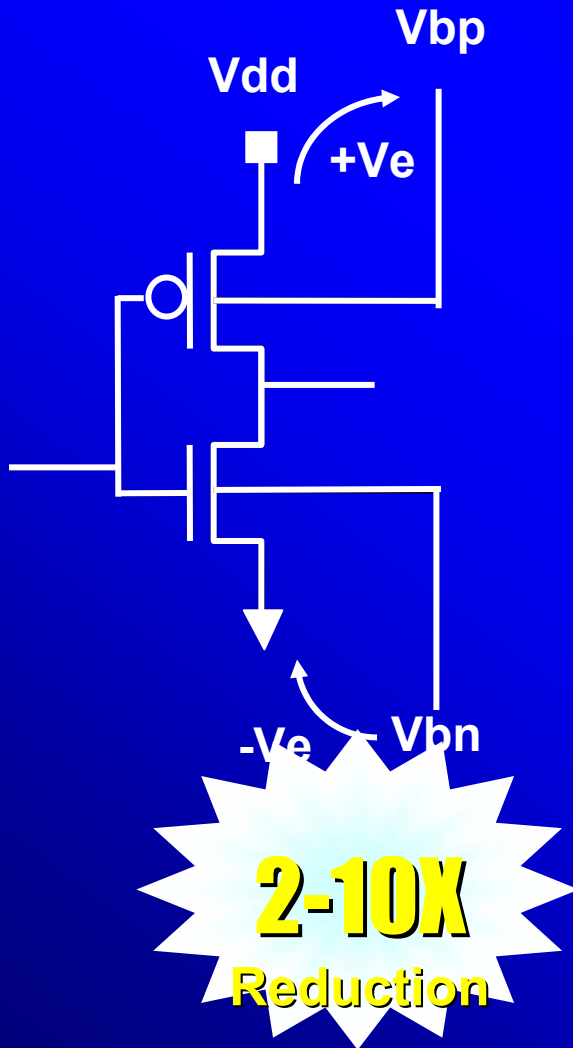
Multiple Supply Voltages

Throughput Oriented Designs

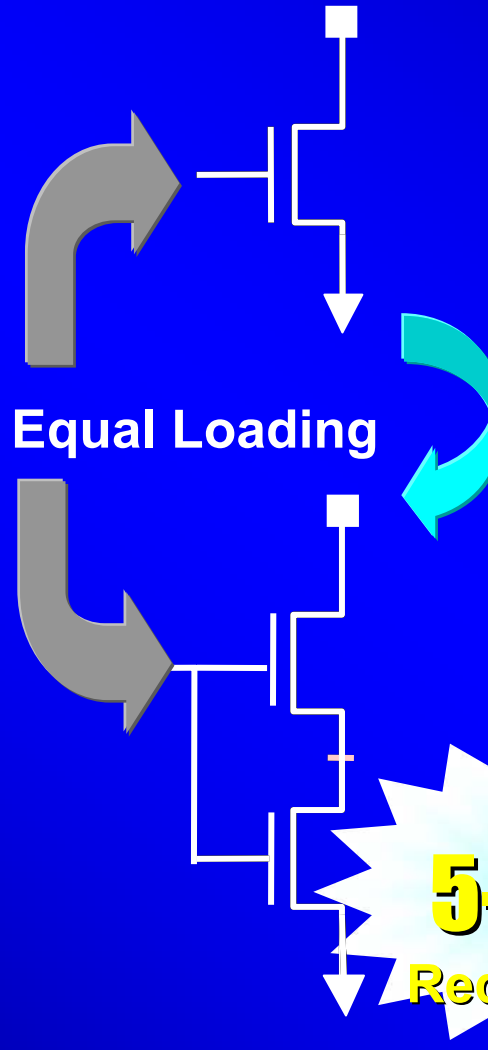


Leakage Control

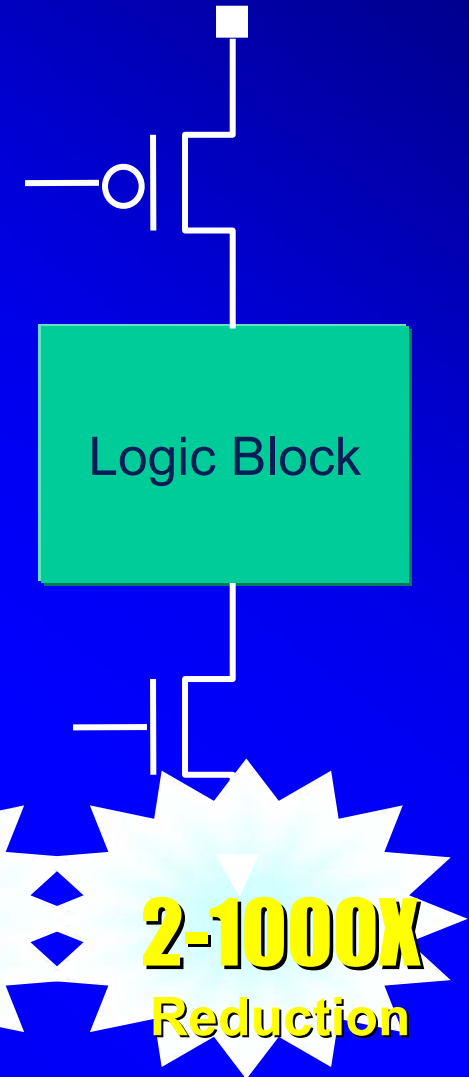
Body Bias



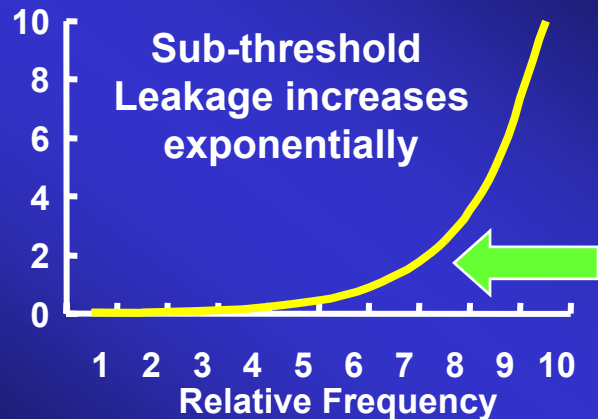
Stack Effect



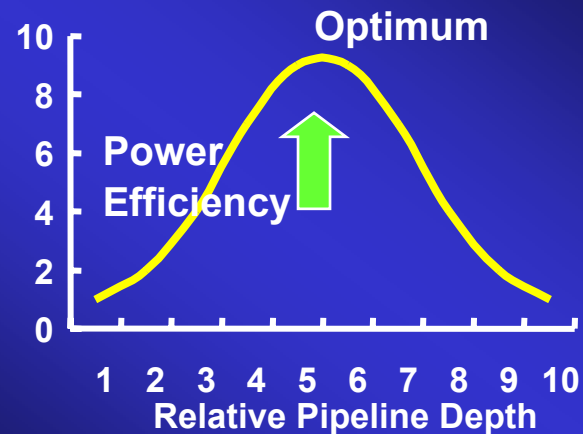
Sleep Transistor



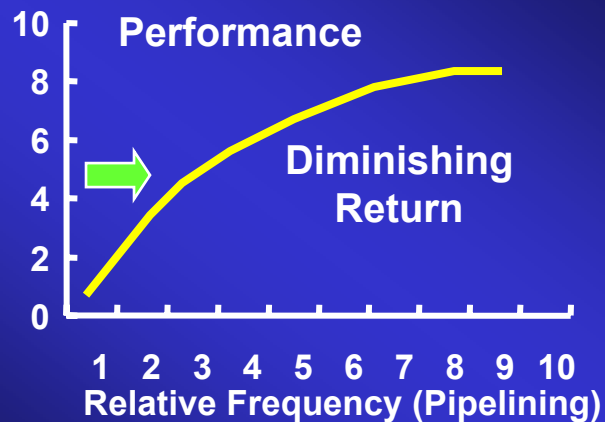
Optimum Frequency



Process Technology



Pipeline Depth



Pipeline & Performance

- Maximum performance with**
- **Optimum pipeline depth**
 - **Optimum frequency**

μArchitecture Techniques

Multi-threading

Single Thread

Full HW Utilization

ST

Wait for Mem

Multi-Threading

MT1

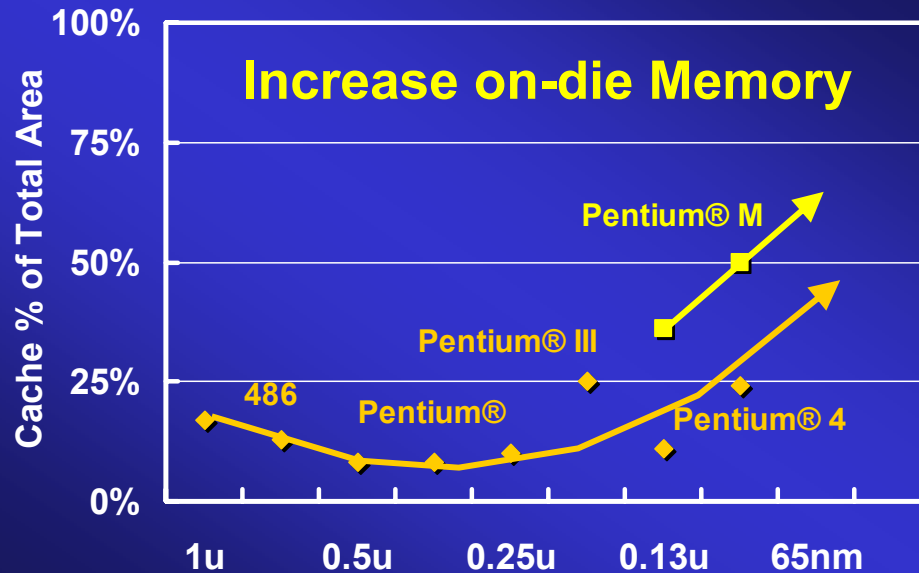
Wait for Mem

MT2

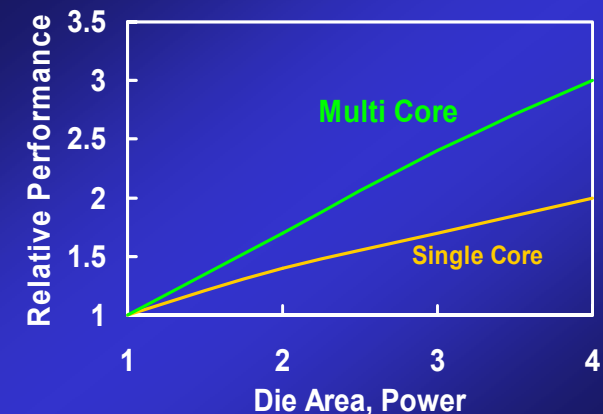
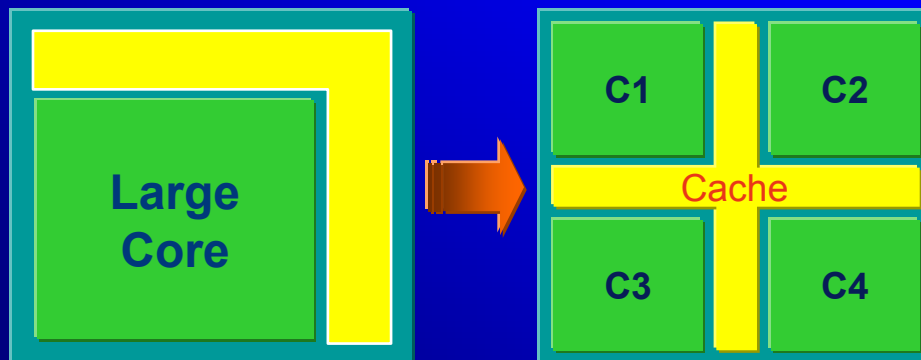
Wait

MT3

Improved performance, no impact on thermals & power delivery

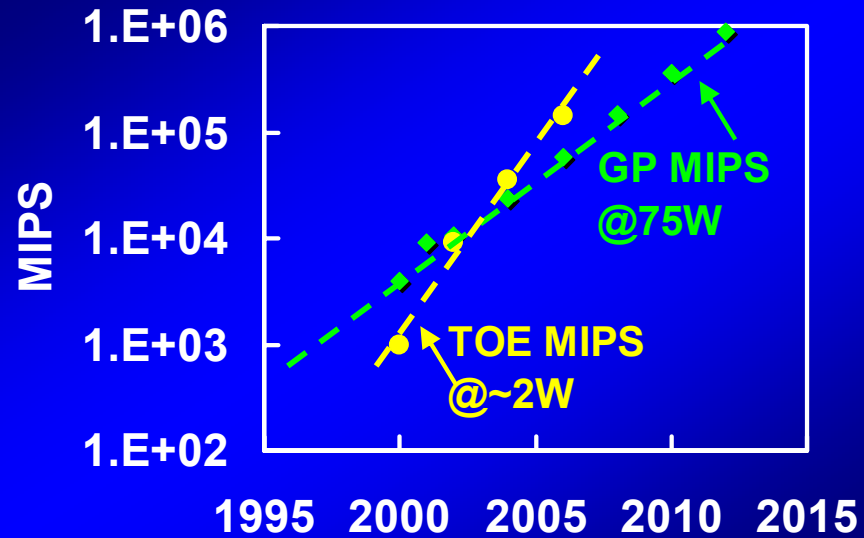
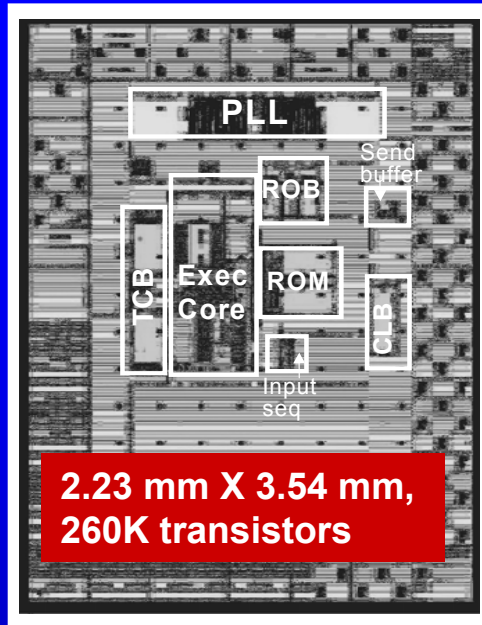


Chip Multi-processing



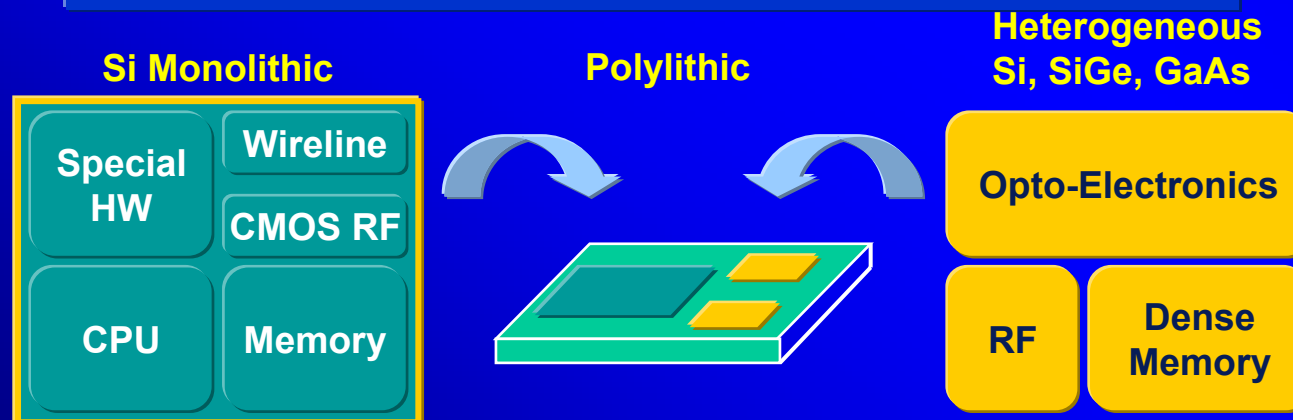
Special Purpose Hardware

TCP/IP Offload Engine



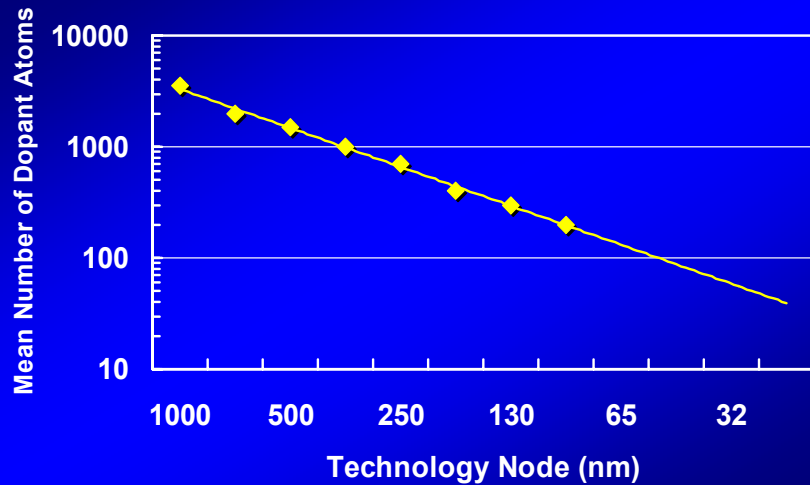
Opportunities: Network processing engines
MPEG Encode/Decode engines, Speech engines

Special purpose HW and extreme integration

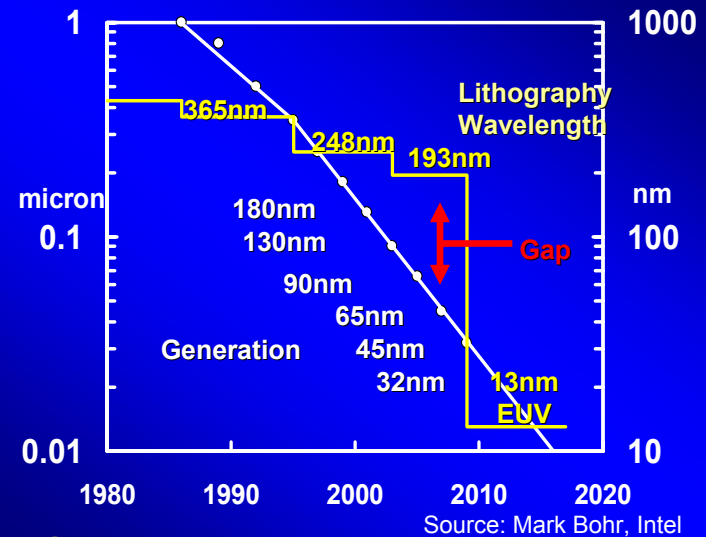


Variations

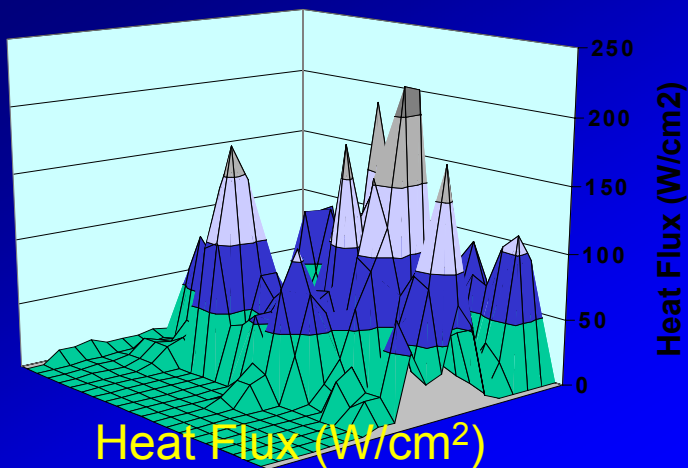
Sources of Variations



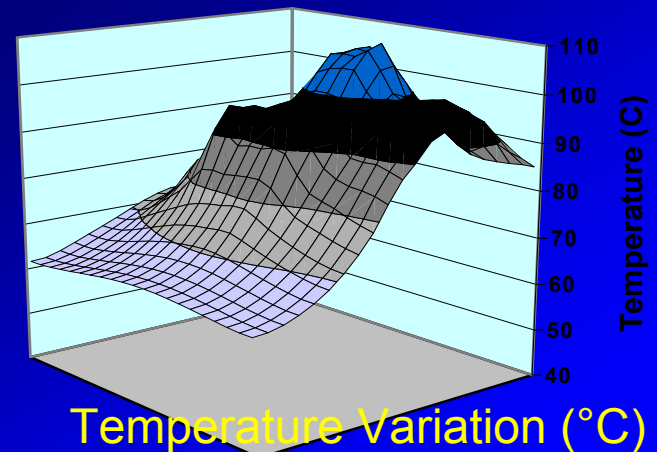
Random Dopant Fluctuations



Sub-wavelength Lithography

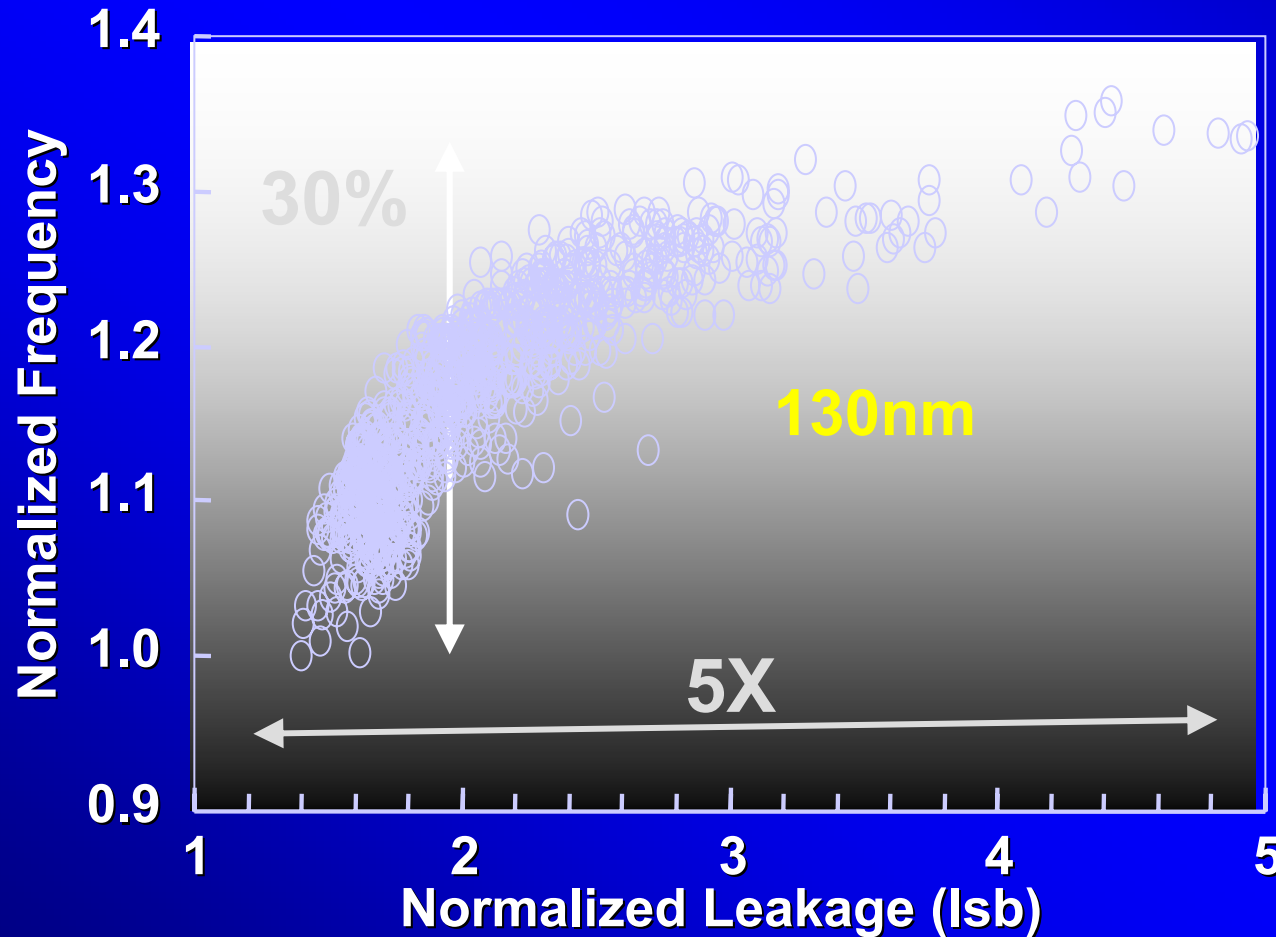


Heat Flux (W/cm^2)
Results in Vcc variation



Temperature Variation ($^{\circ}\text{C}$)
Hot spots

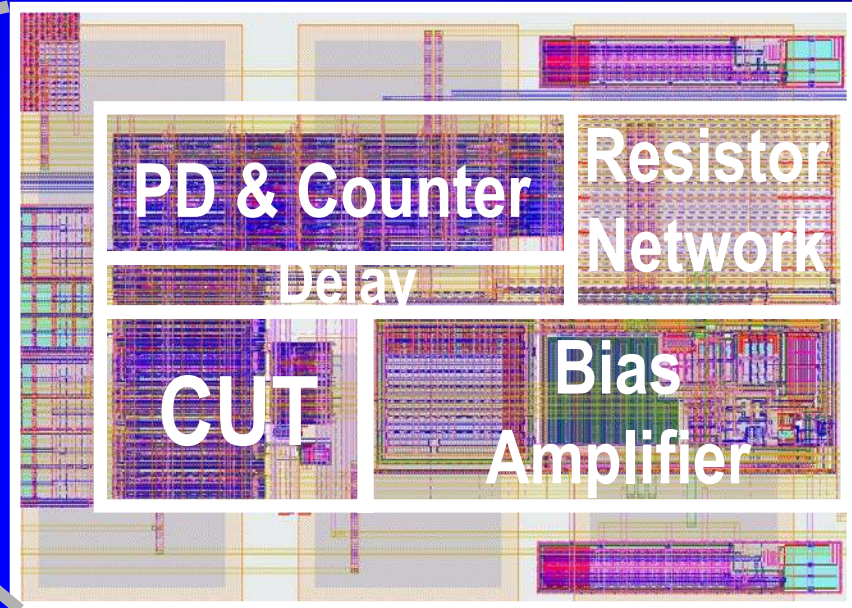
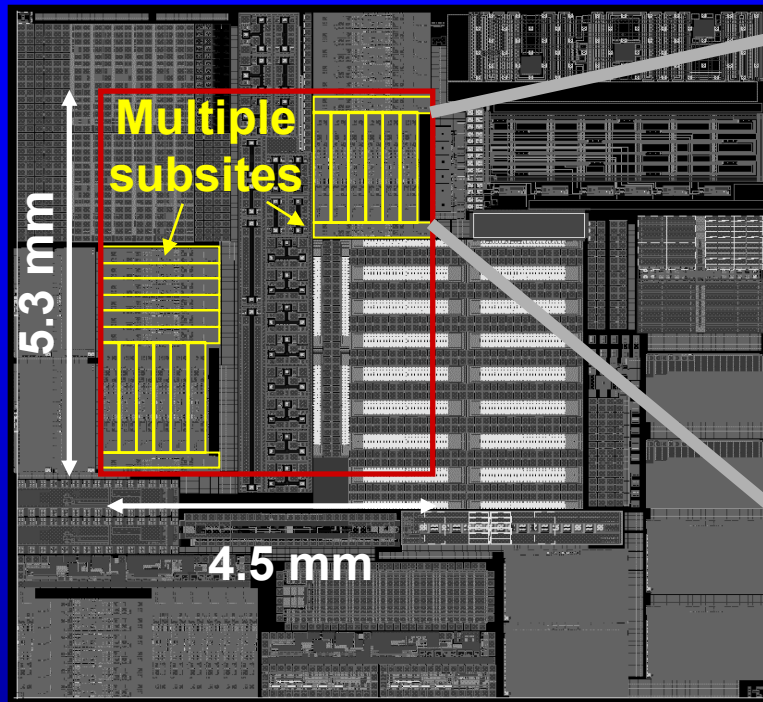
Impact of Static Variations *Today...*



Frequency
~30%

Leakage Power
~5-10X

Adaptive Body Bias--Experiment



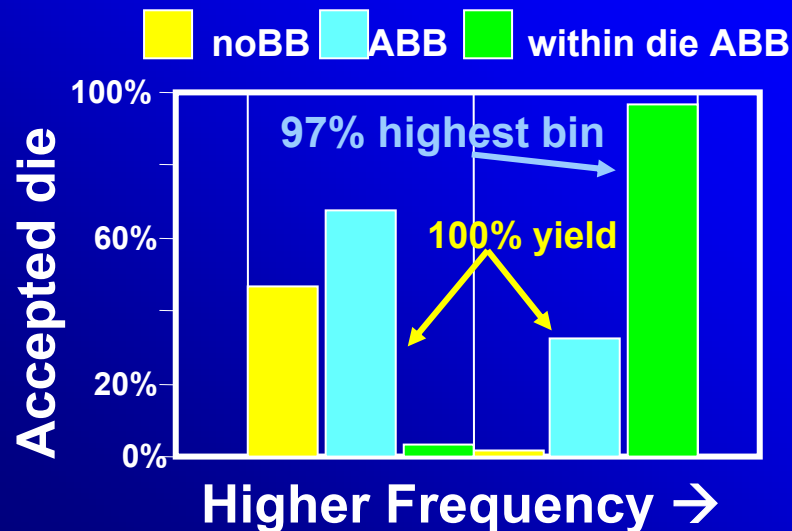
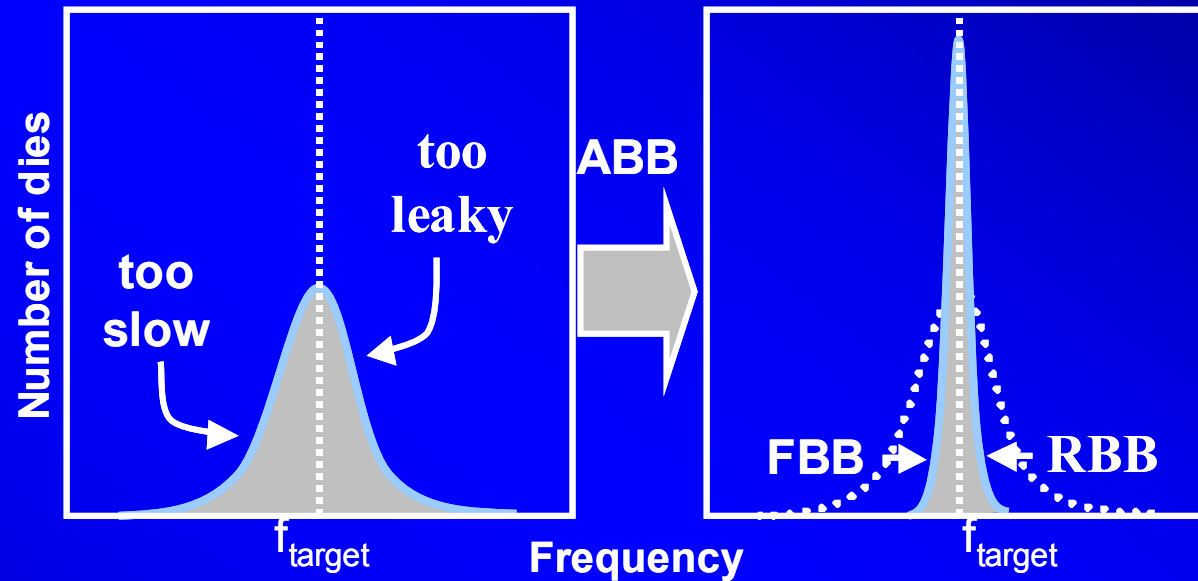
1.6 X 0.24 mm, 21 sites per die
150nm CMOS

Technology	150nm CMOS
Number of subsites per die	21
Body bias range	0.5V FBB to 0.5V RBB
Bias resolution	32 mV

Die frequency: $\text{Min}(F_1..F_{21})$

Die power: $\text{Sum}(P_1..P_{21})$

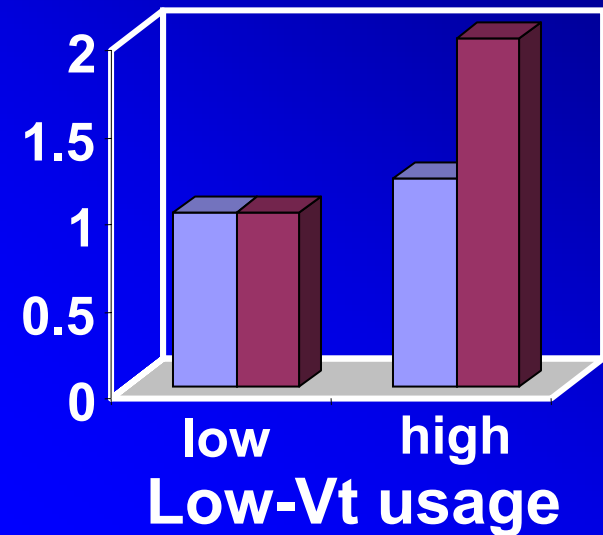
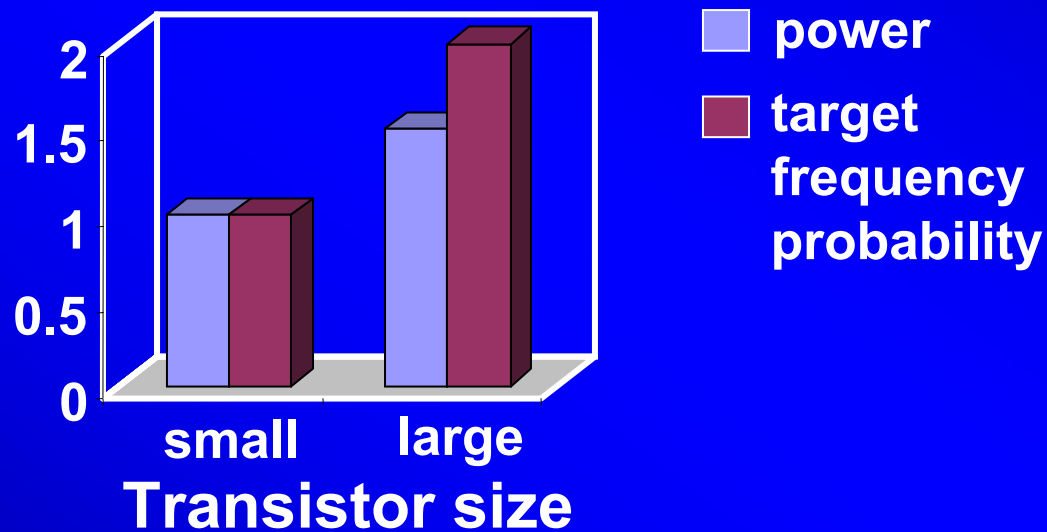
Adaptive Body Bias--Results



For given Freq and Power density

- 100% yield with ABB
- 97% highest freq bin with ABB for within die variability

Circuit Design Tradeoffs

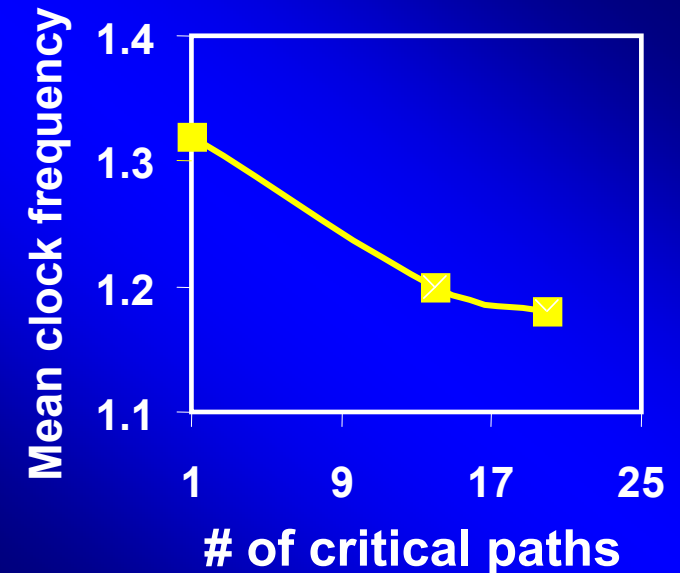
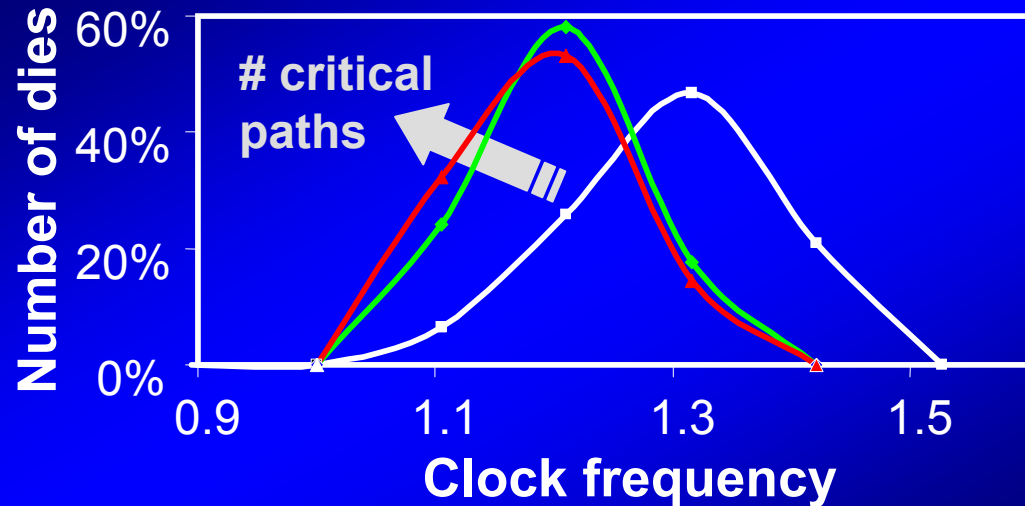


Higher probability of target frequency with:

1. Larger transistor sizes
2. Higher Low-Vt usage

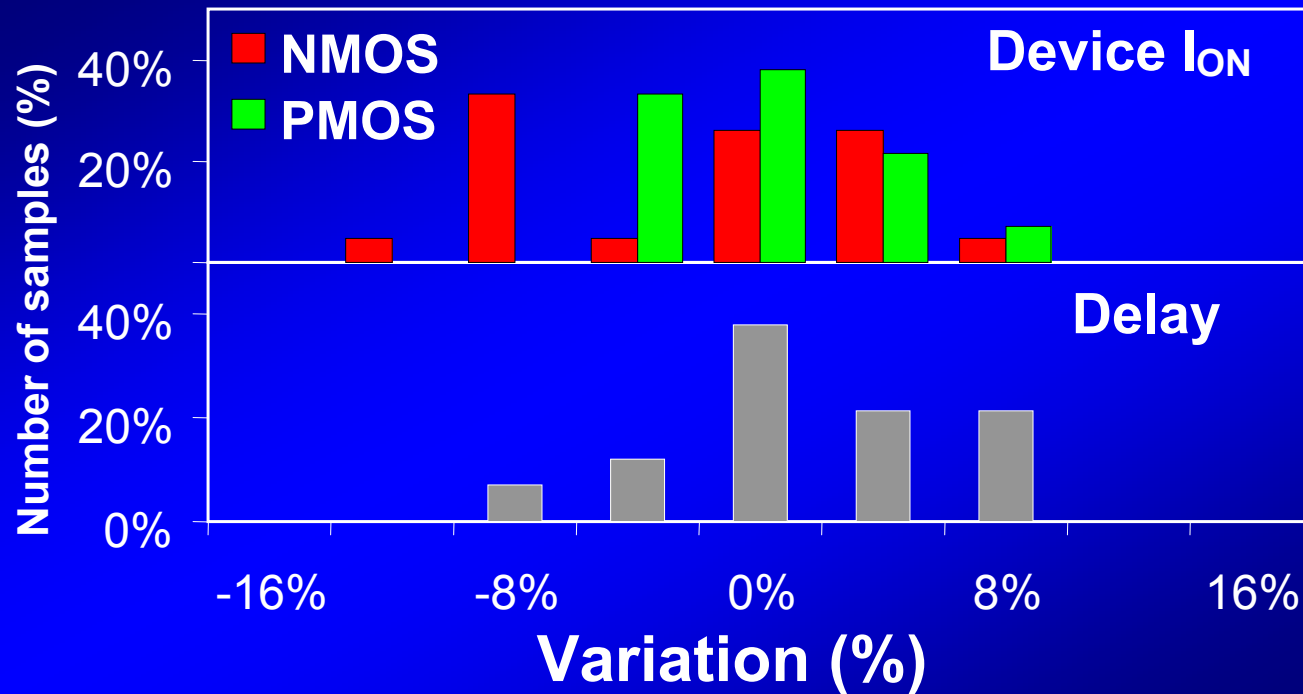
But with power penalty

Impact of Critical Paths

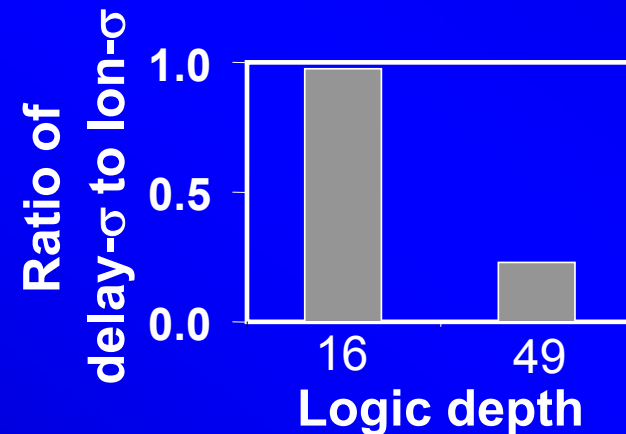


- With increasing # of critical paths
 - Both σ and μ become smaller
 - Lower mean frequency

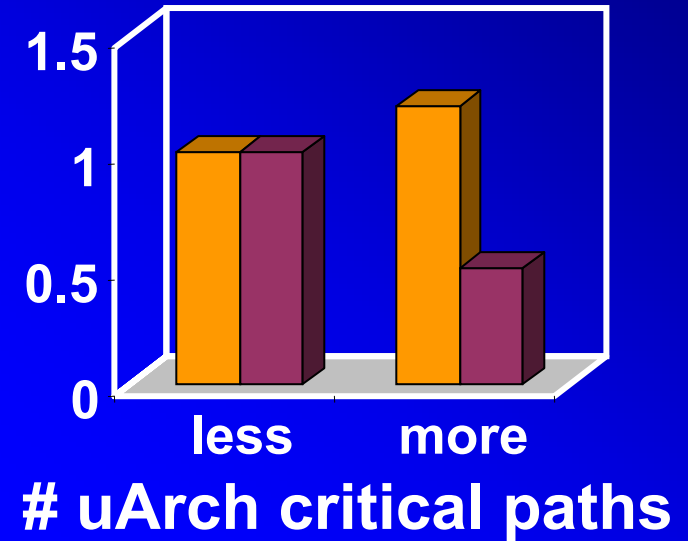
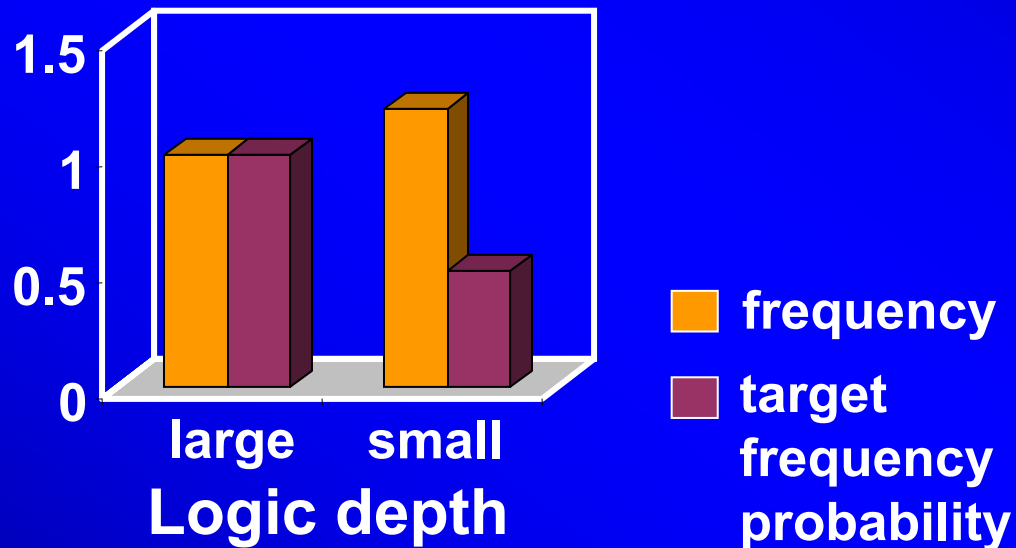
Impact of Logic Depth



Logic depth: 16		
NMOS I _{on}	PMOS I _{on}	Delay
σ/μ	σ/μ	σ/μ
5.6%	3.0%	4.2%



μ Architecture Tradeoffs

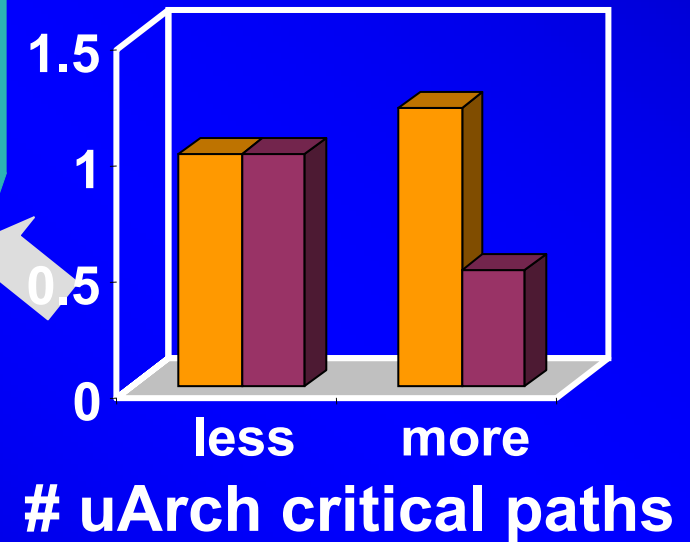
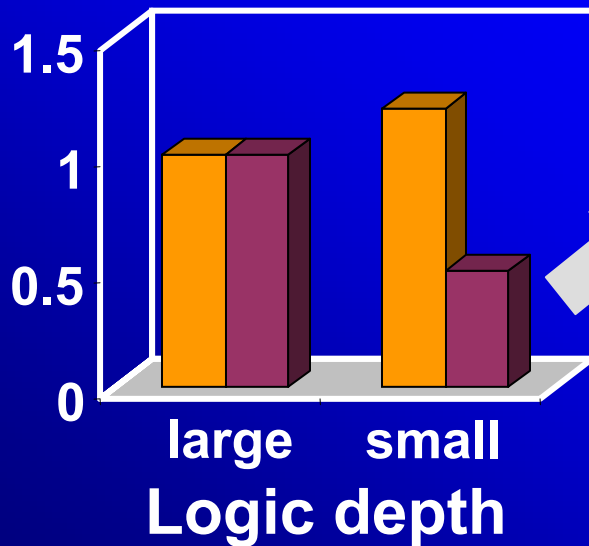
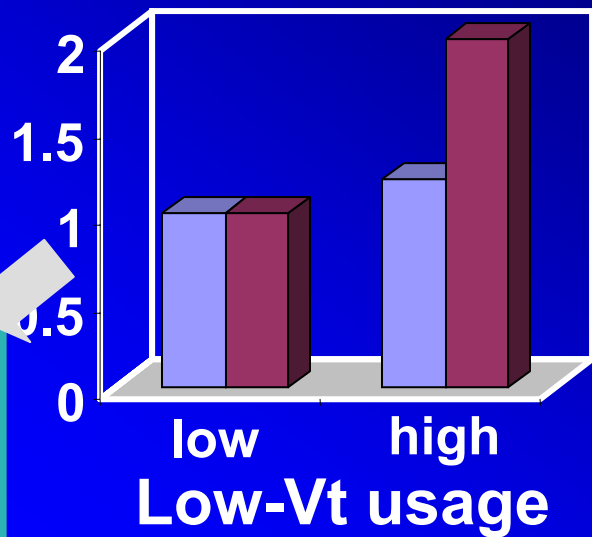
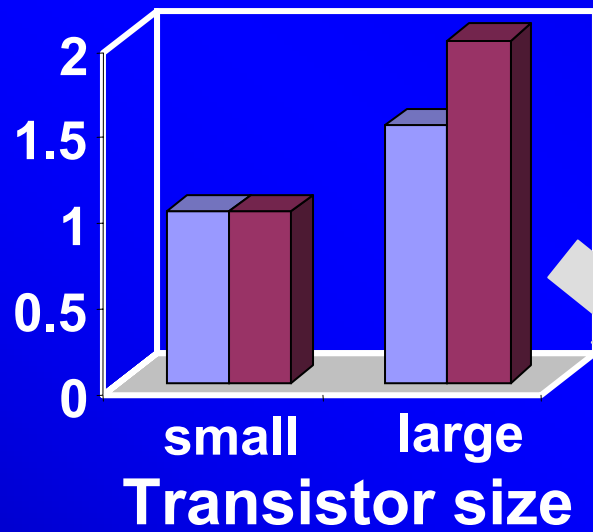


Higher target frequency with:

1. Shallow logic depth
2. Larger number of critical paths

But with lower probability

Variation-tolerant Design

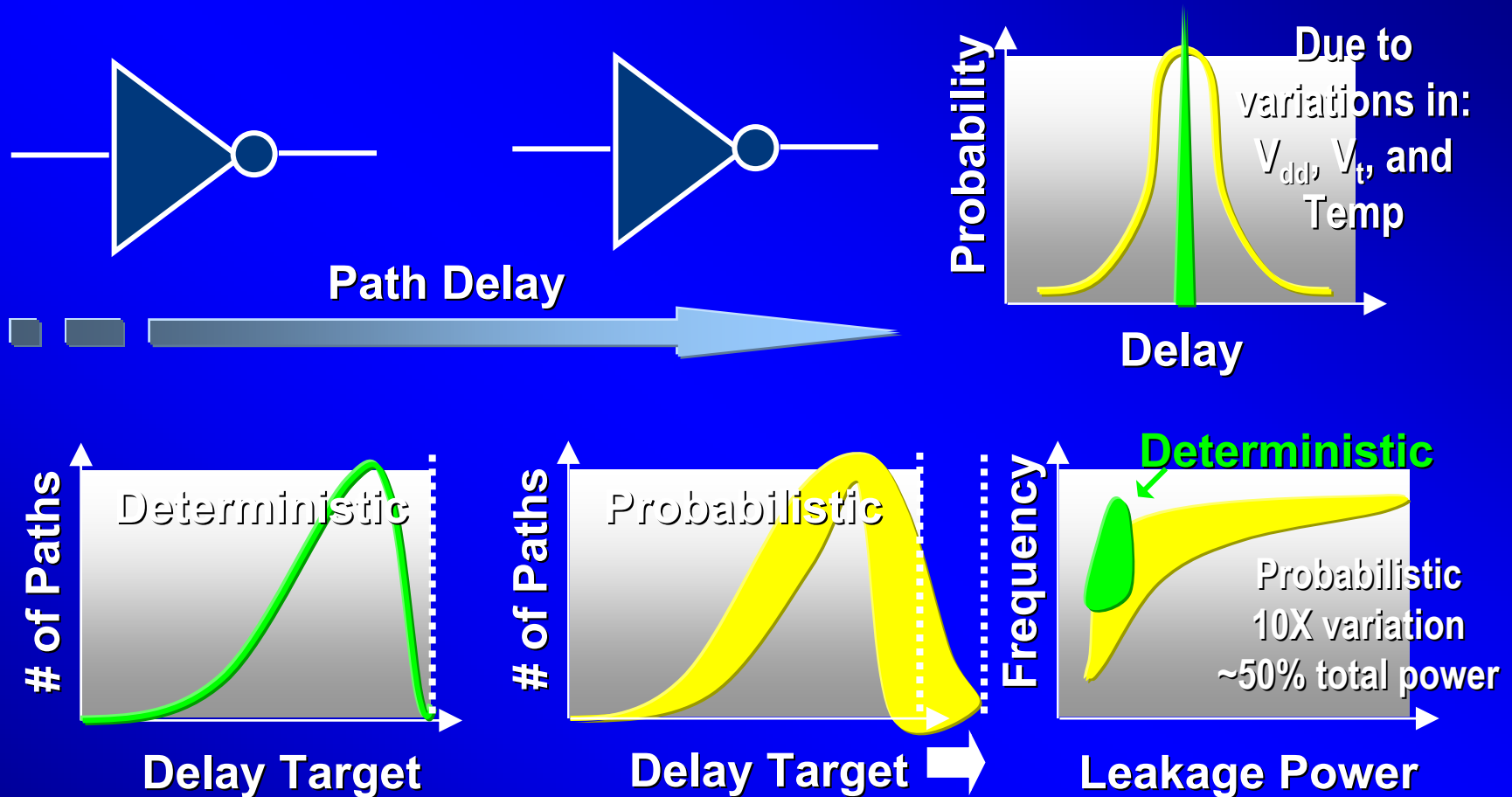


power
target frequency probability

Balance power & frequency with variation tolerance

frequency
target frequency probability

Probabilistic Design



Deterministic design techniques inadequate in the future

Shift in Design Paradigm

- Multi-variable design optimization for:
 - Yield and bin splits
 - Parameter variations
 - Active and leakage power
 - Performance

Today:

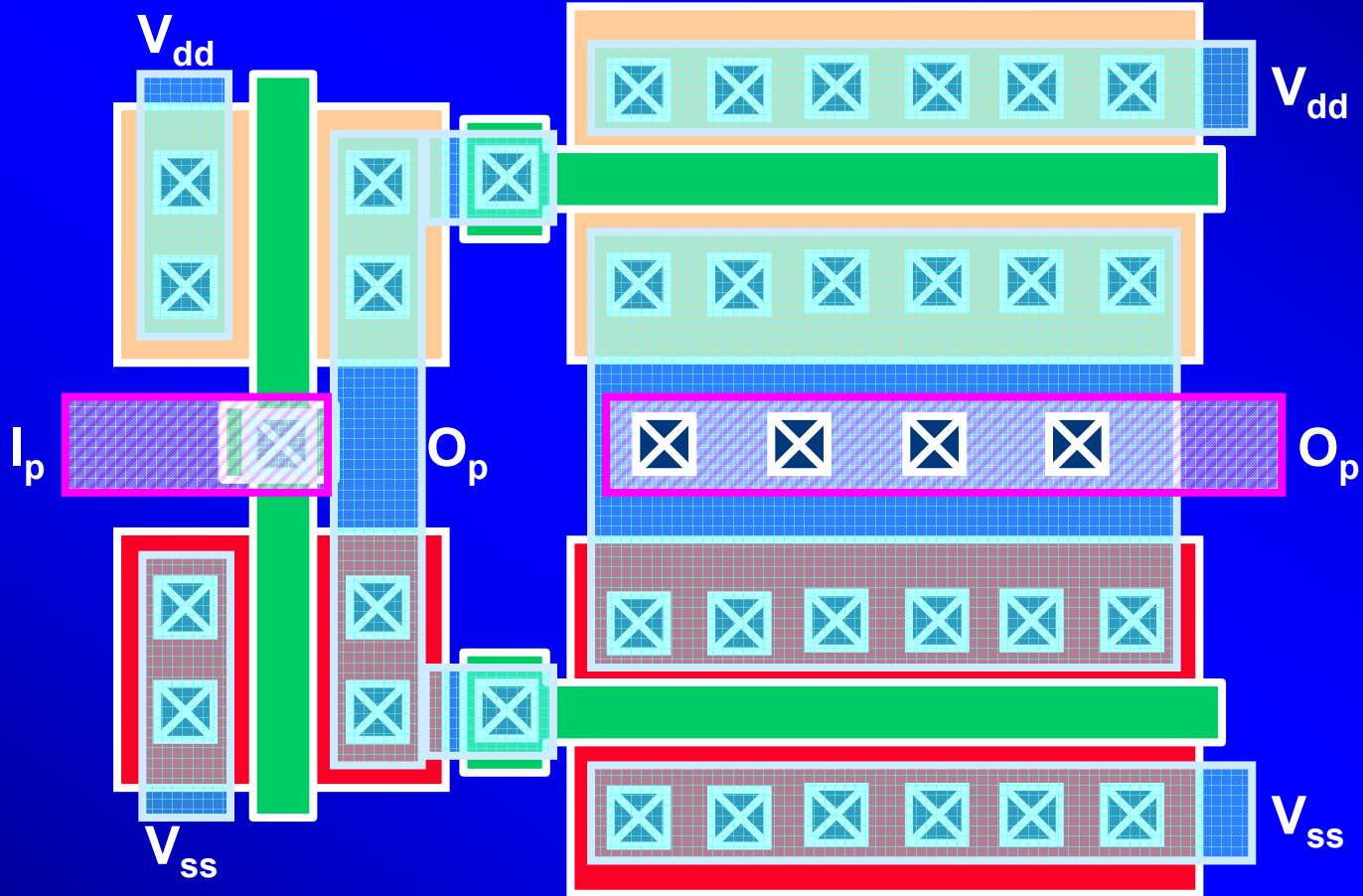
Local Optimization
Single Variable

Tomorrow:

Global Optimization
Multi-variate

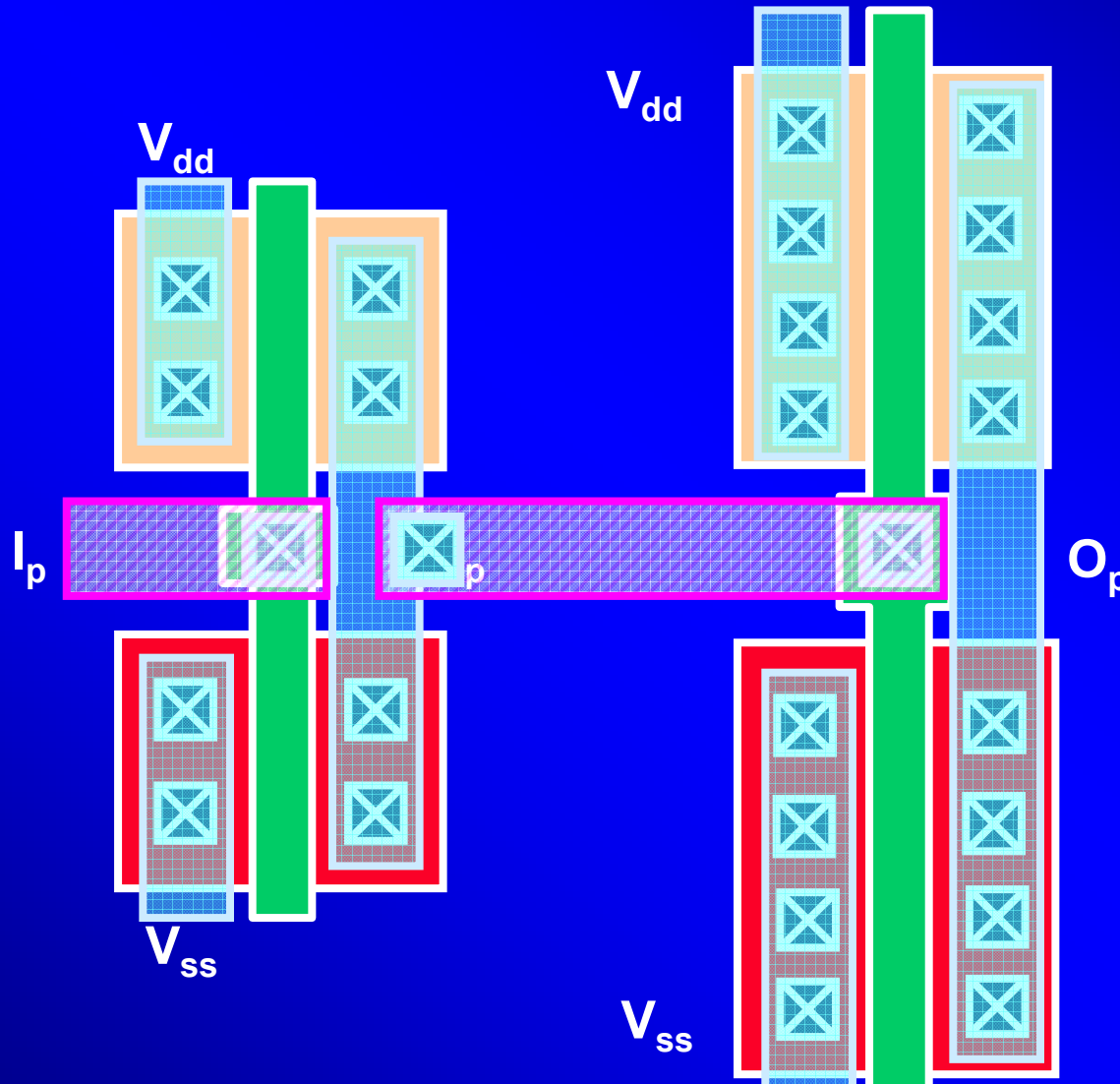
Physical Design

Today's Freelance Layout



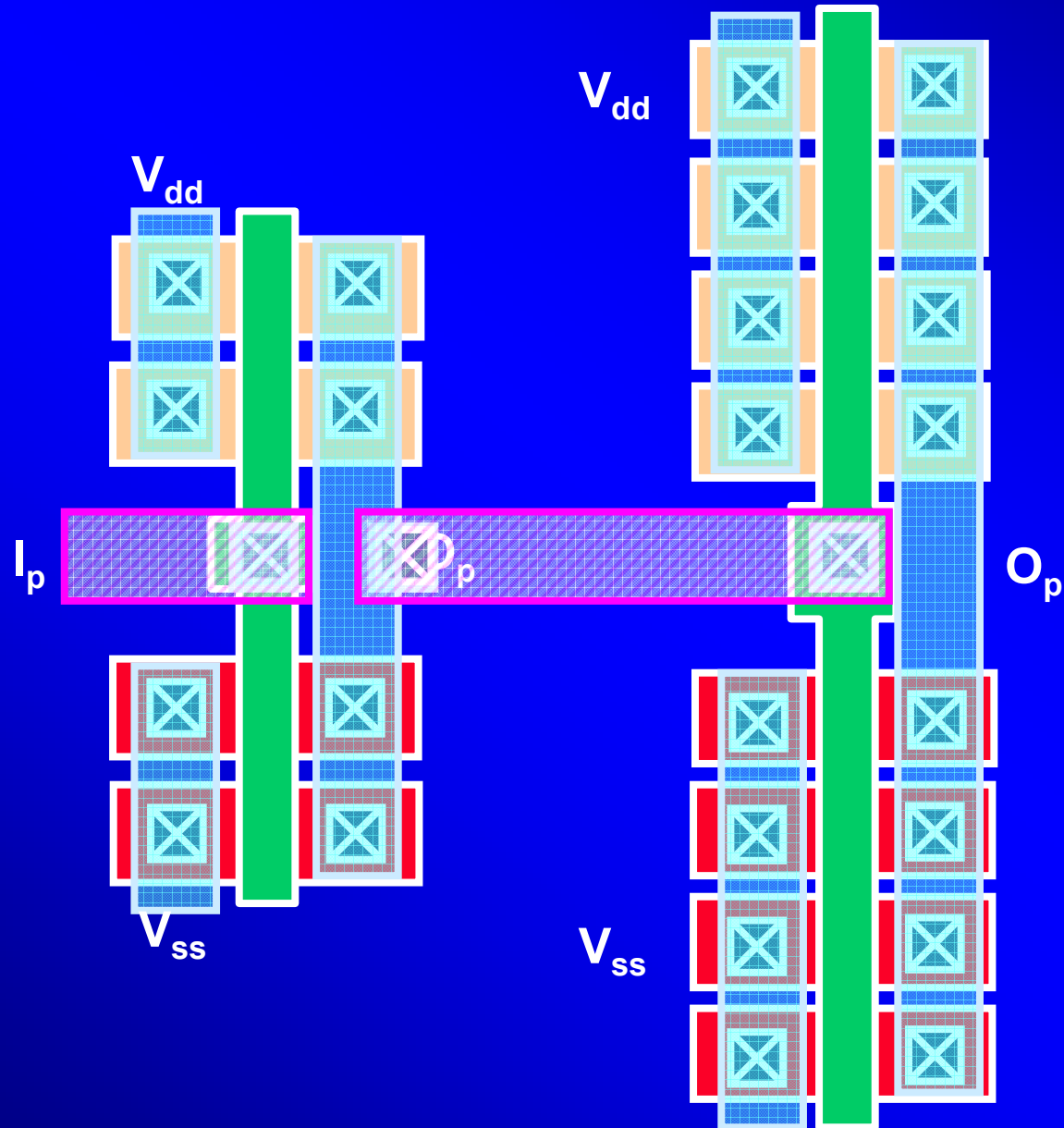
No layout restrictions

Transistor Orientation Restrictions

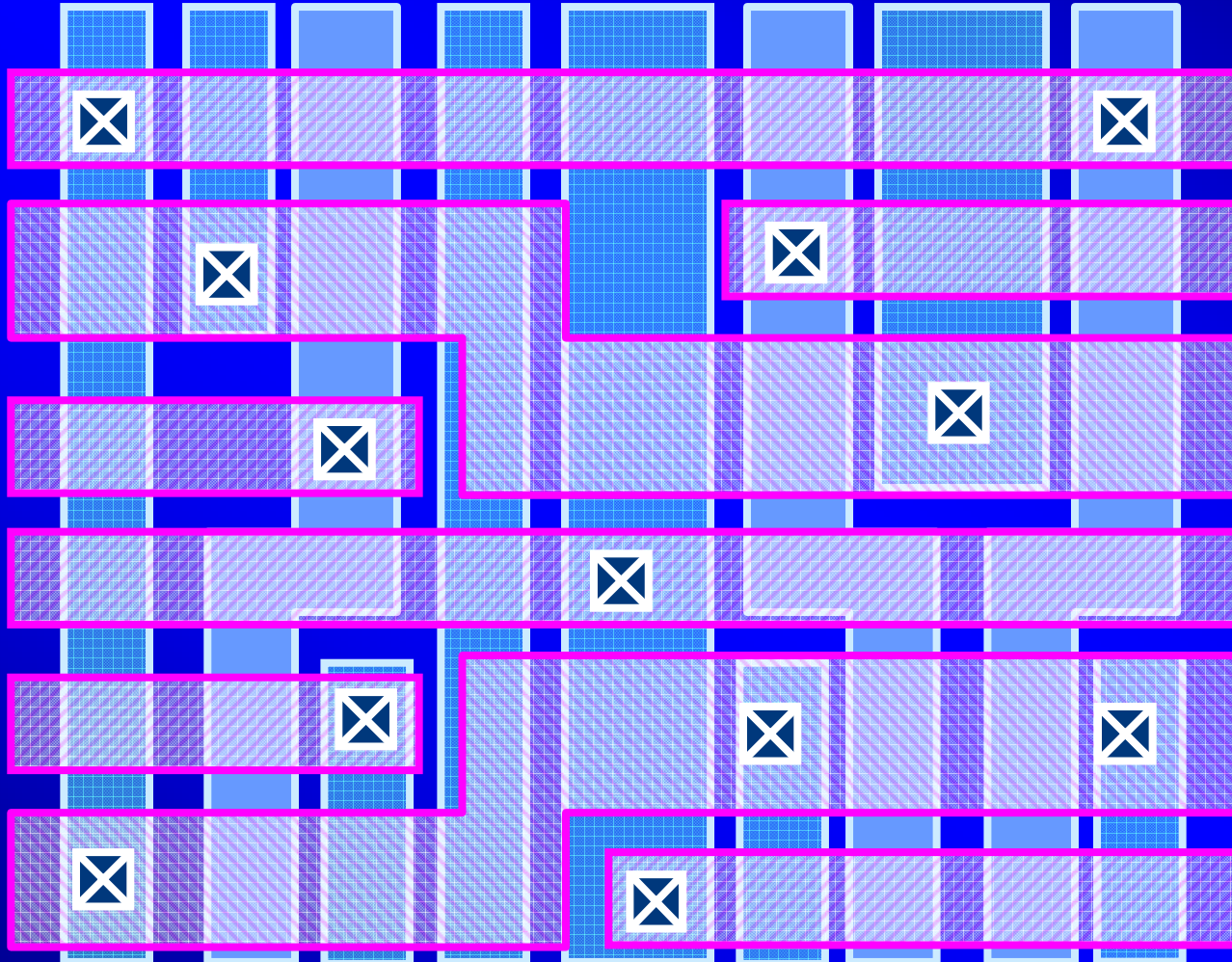


Transistor orientation restricted to improve manufacturing control

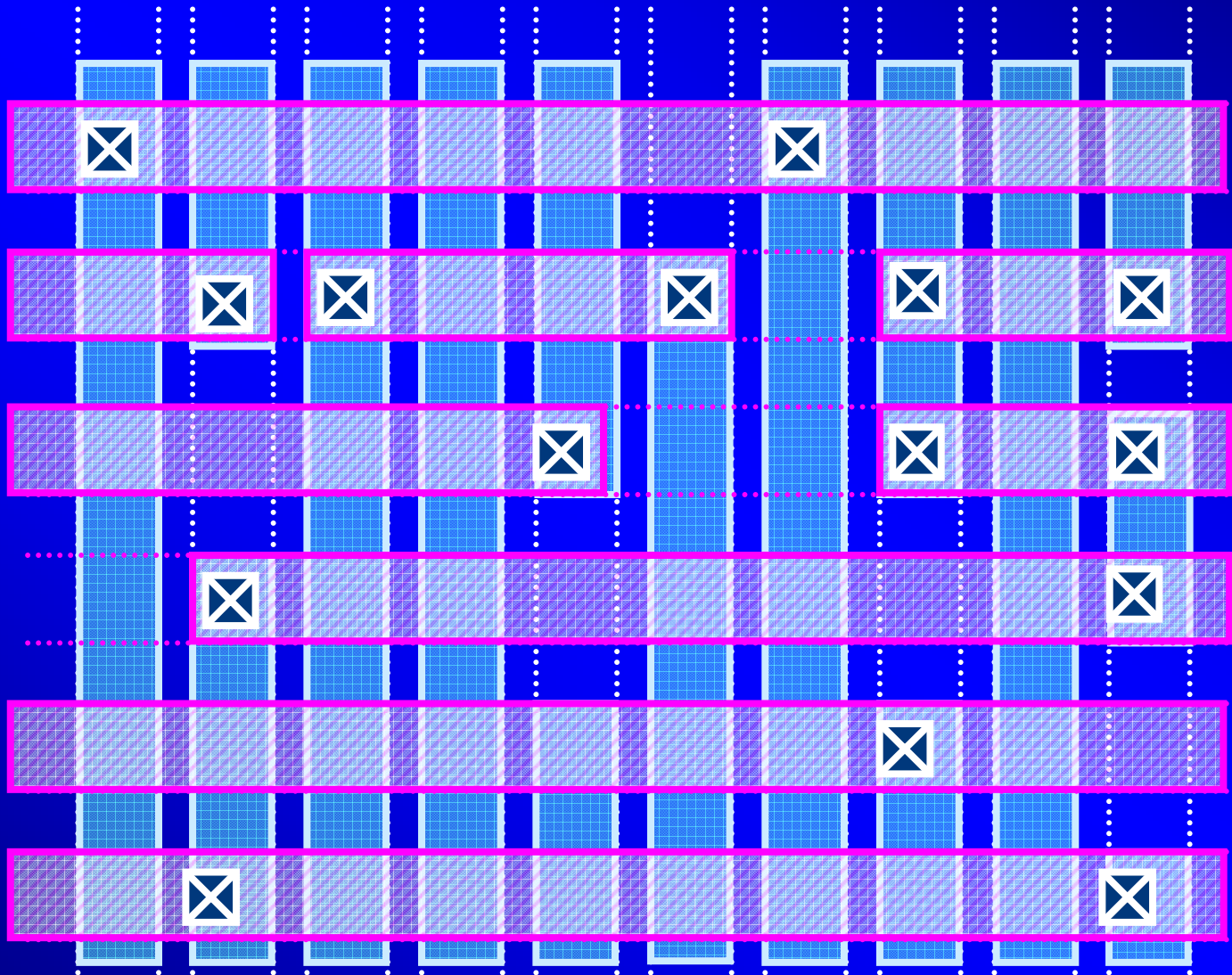
Transistor Width Quantization



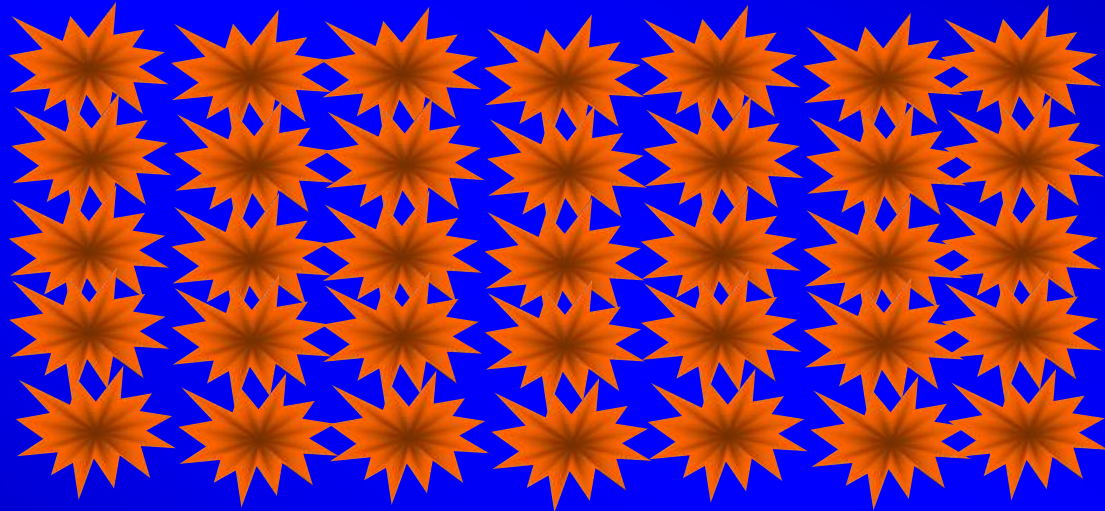
Today's Unrestricted Routing



Future Metal Restrictions

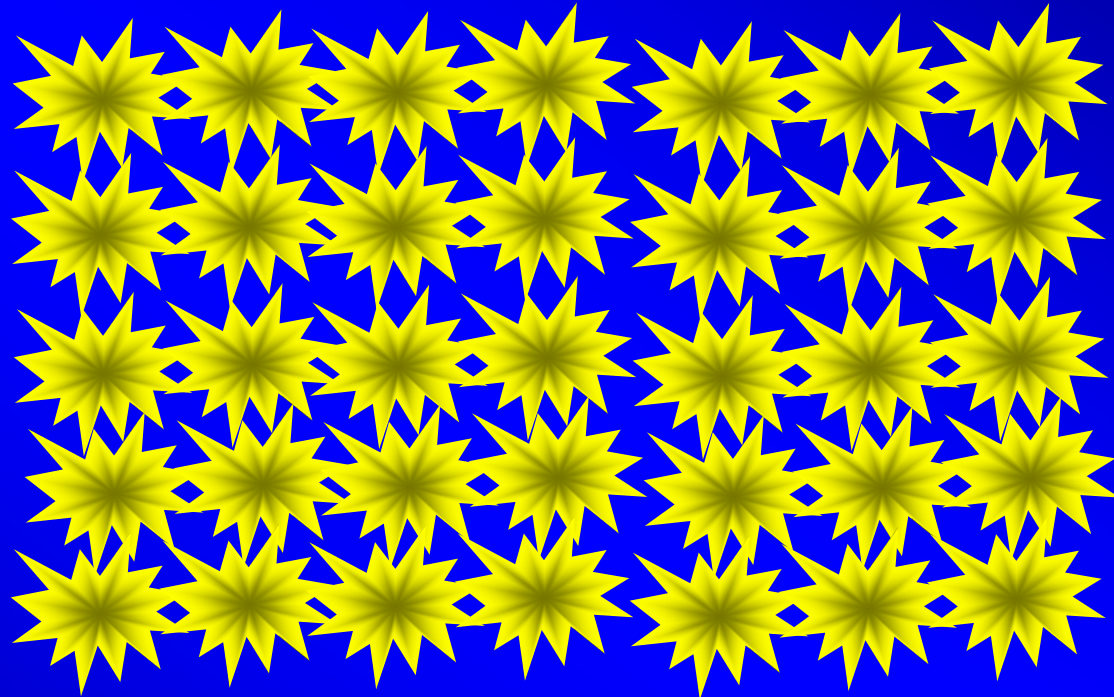


Today's Metric: Maximizing Transistor Density



Dense layout causes hot-spots

Tomorrow's Metric: Optimizing Transistor & Power Density



Balanced Design

Implications to Design

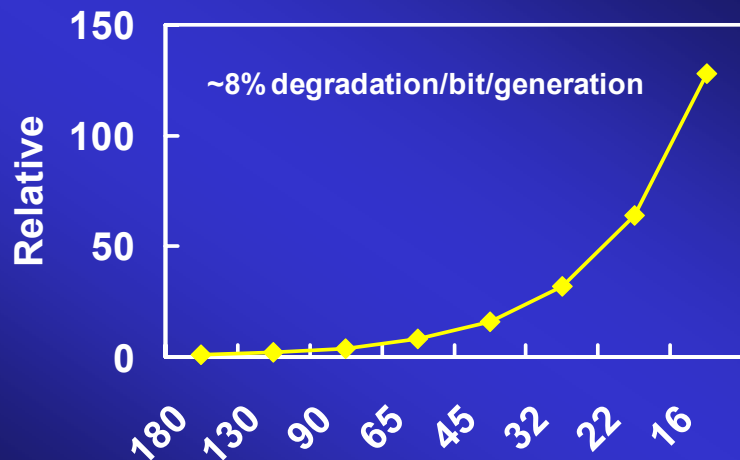
- Design fabric will be *Regular*
- Will look like *Sea-of-transistors* interconnected with regular interconnect fabric
- Shift in the design efficiency metric
 - From *Transistor Density* to *Balanced Design*

Extreme Variations

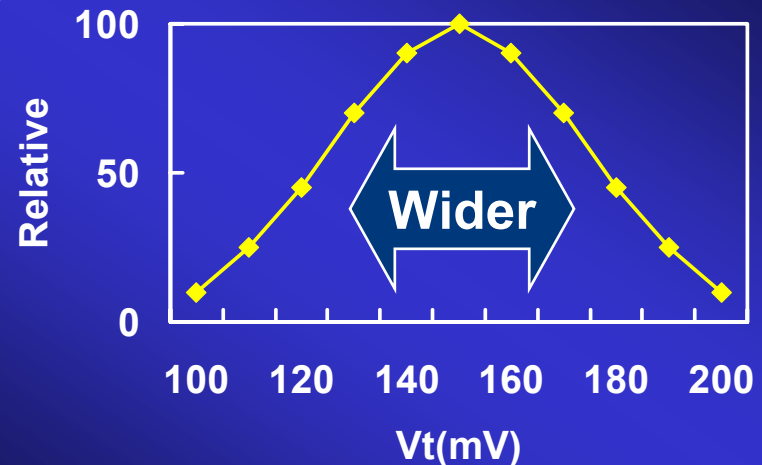
Technology Outlook

High Volume Manufacturing	2004	2006	2008	2010
Technology Node (nm)	90	65	45	32
Integration Capacity (BT)	2	4	8	16
Delay = CV/I scaling	0.7	~0.7	>0.7	Delay
Energy/Logic Op scaling	>0.35	>0.5	>0.5	Energy
Bulk Planar CMOS	High Probability			
Alternate, 3G etc	Low Probability			
Variability	Medium		High	
ILD (K)	~3	<3	Reduced	
RC Delay	1	1	1	1
Metal Layers	6-7	7-8	8-9	0.5

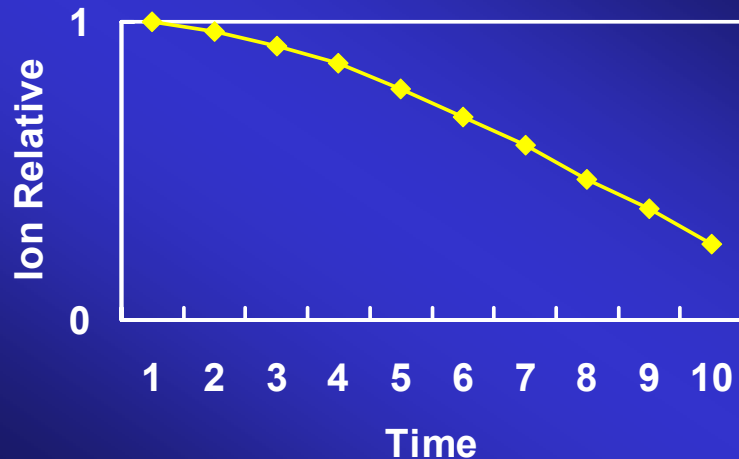
Reliability



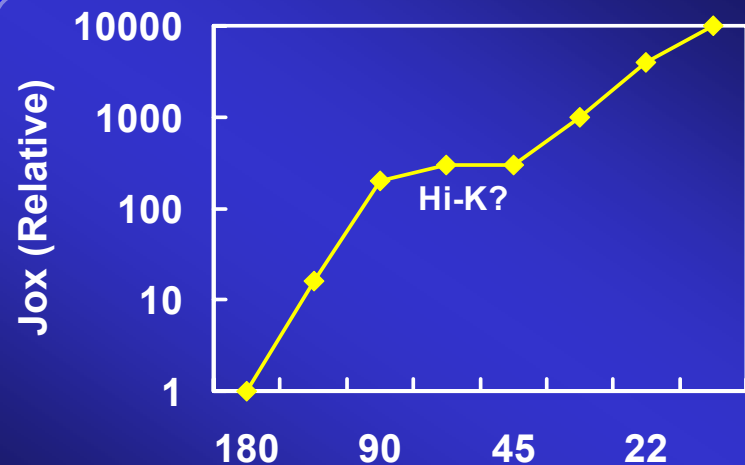
Soft Error FIT/Chip (Logic & Mem)



Extreme device variations



Time dependent device degradation



Burn-in may phase out...?

Implications to Reliability

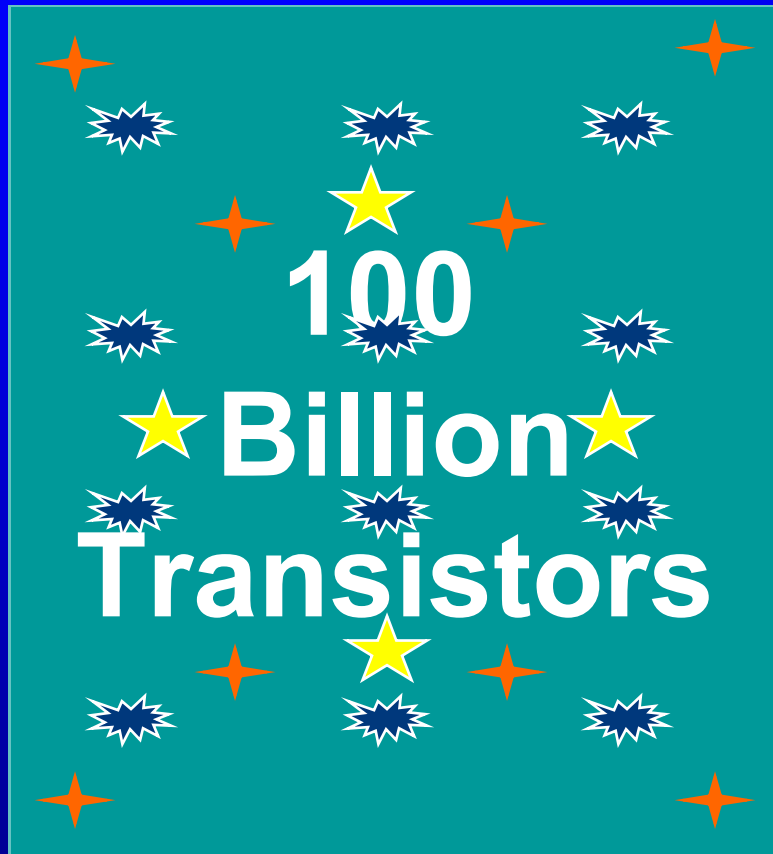
- Extreme variations (Static & Dynamic) will result in unreliable components
- Impossible to design reliable system as we know today
 - Transient errors (Soft Errors)
 - Gradual errors (Variations)
 - Time dependent (Degradation)

Reliable systems with unreliable components
—Resilient μ Architectures

Implications to Test

- One-time-factory testing will be out
- Burn-in to catch chip infant-mortality will not be practical
- Test HW will be part of the design
- Dynamically self-test, detect errors, reconfigure, & adapt

In a Nut-shell...



100 BT integration capacity

20 BT unusable (variations)

10 BT will fail over time

Intermittent failures

Yet, deliver high performance in the power & cost envelope

Summary (of Challenges)

- **Near term:**
 - Optimum frequency & μ Architecture
 - Lots of memory & Multi—everywhere
 - Valued performance with higher integration
- **Paradigm shift:**
 - From deterministic to probabilistic design, with multi-variate optimization
 - Evolution of regular design fabric
- **Long term:**
 - Reliable systems with unreliable components
 - Dynamic self-test, detect, reconfigure, & adapt